

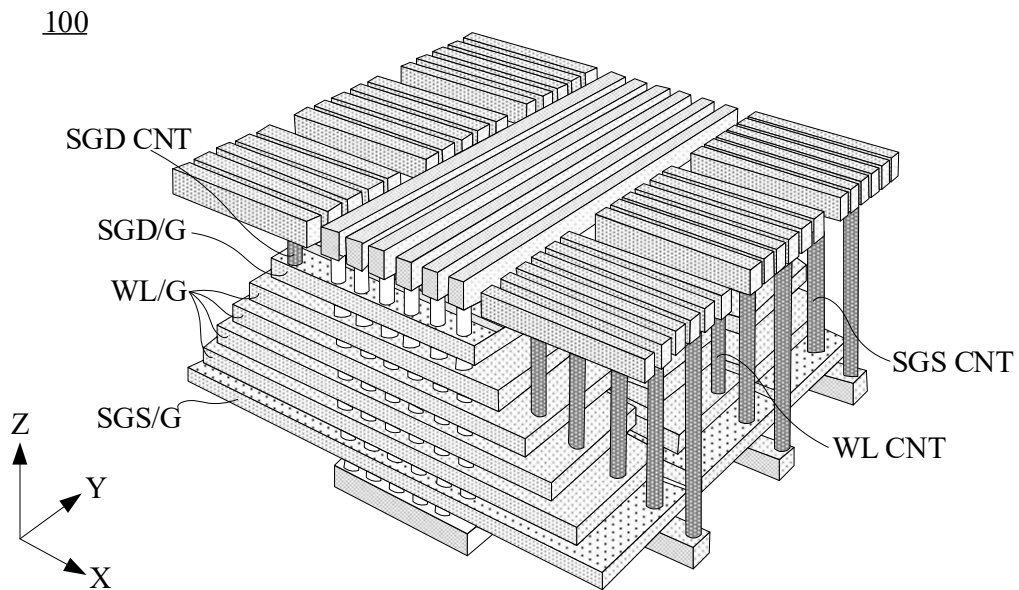


Fig. 1

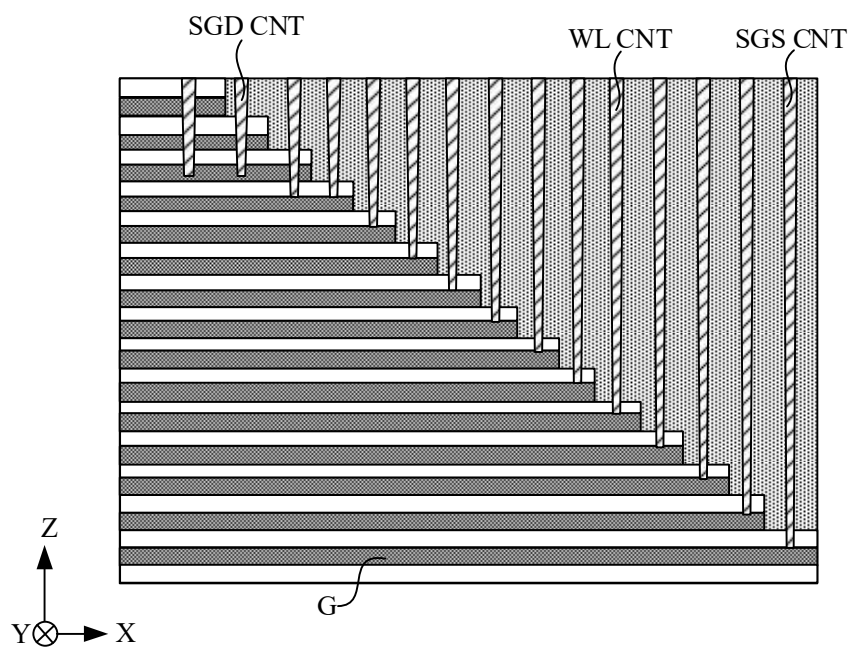


Fig. 2

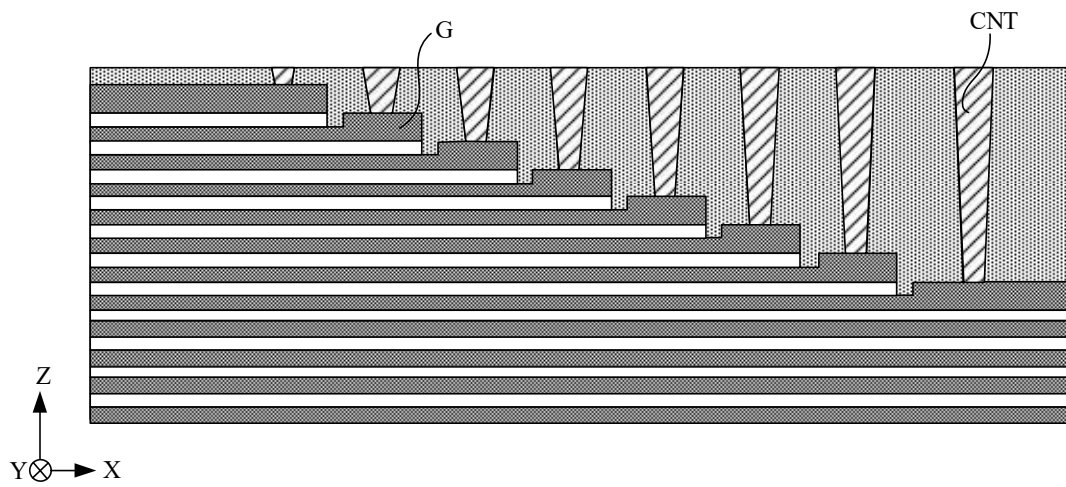


Fig. 3

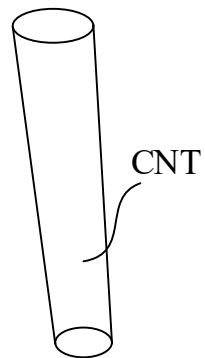


Fig. 4

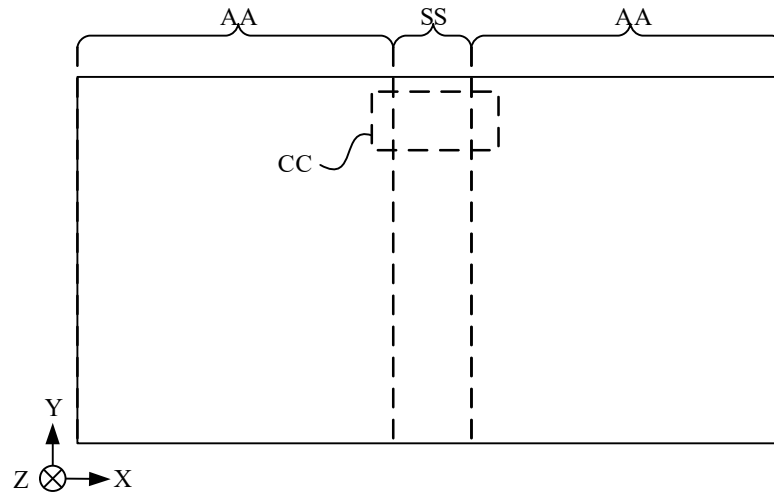
200 (300)

Fig. 5A

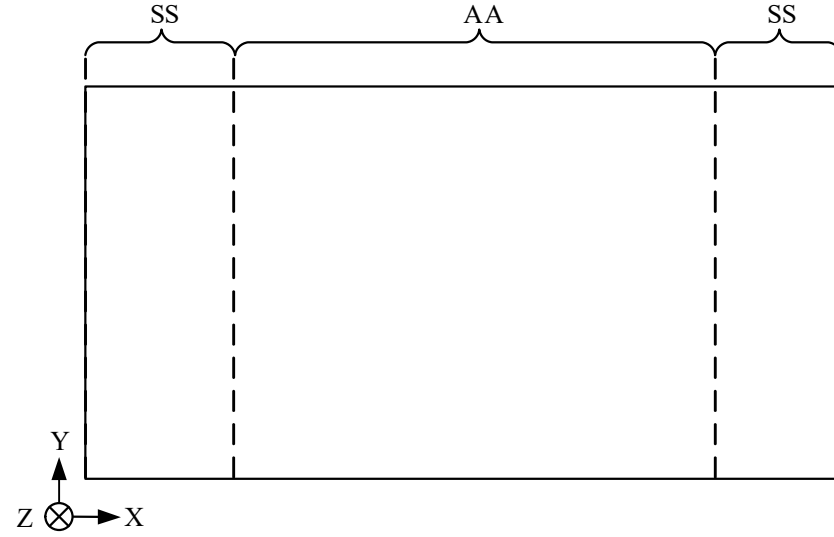
200 (300)

Fig. 5B

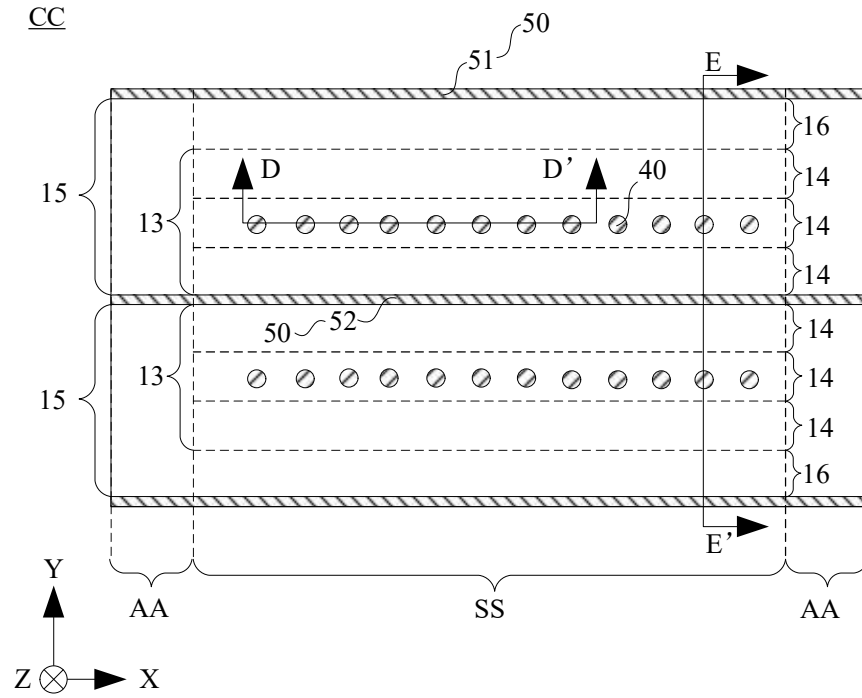


Fig. 6

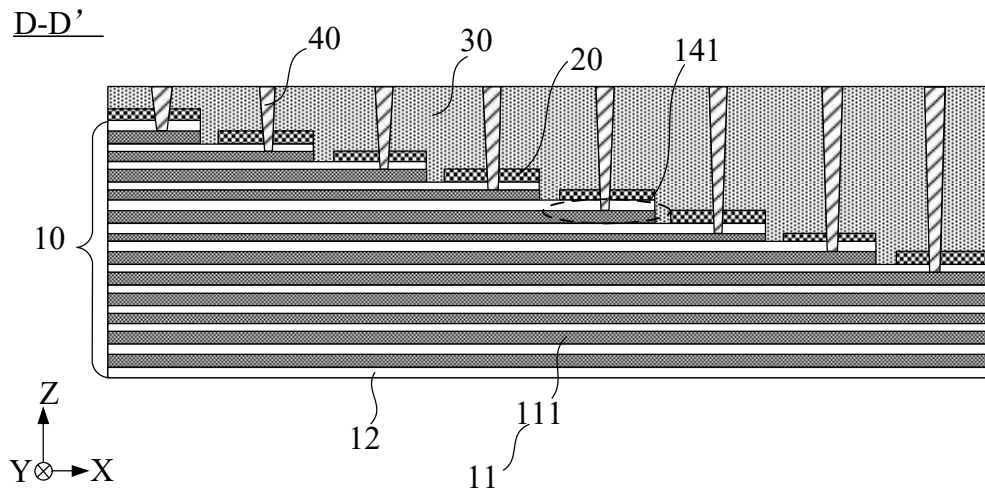


Fig. 7A

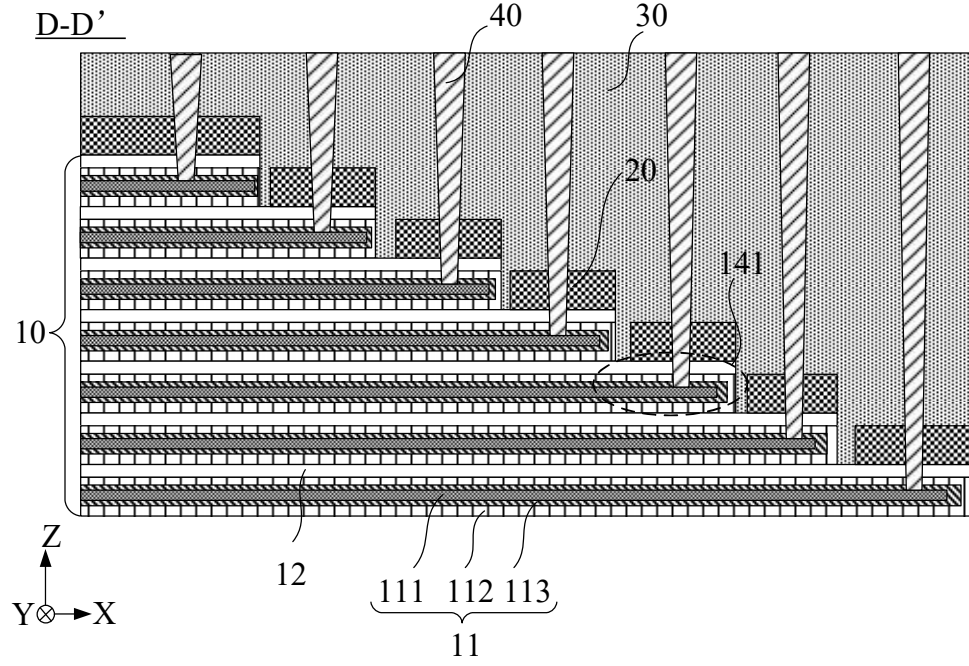


Fig. 7B

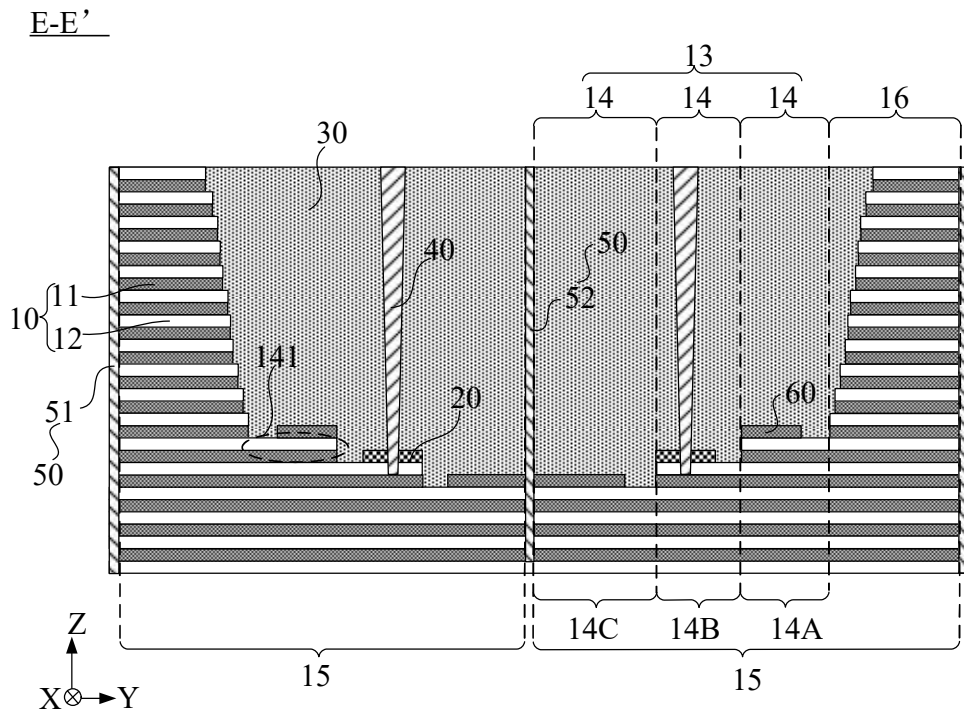


Fig. 8

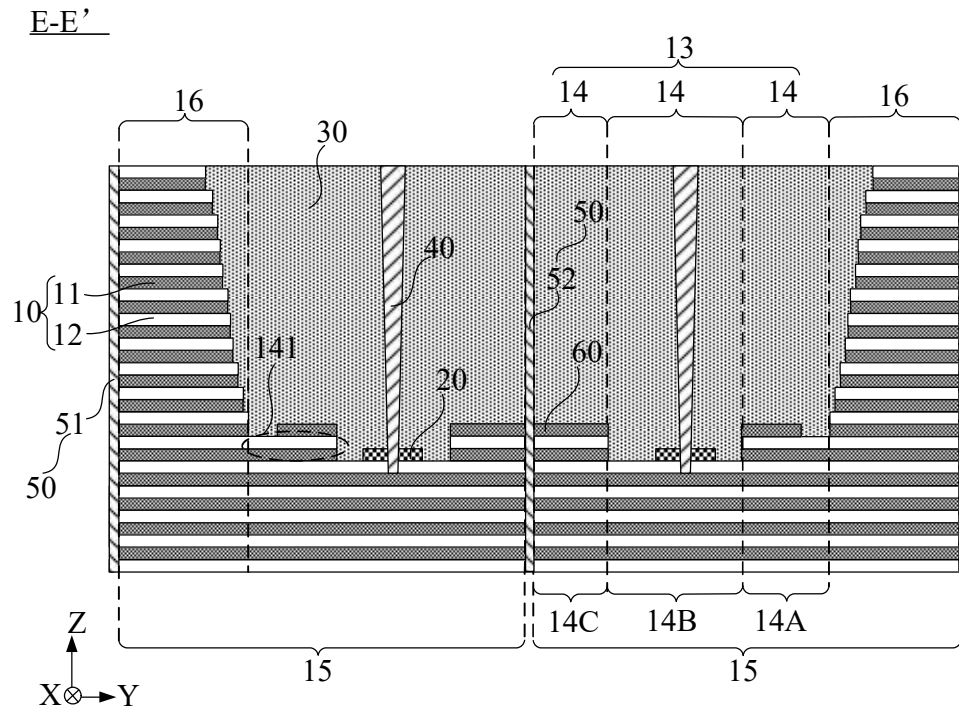


Fig. 9

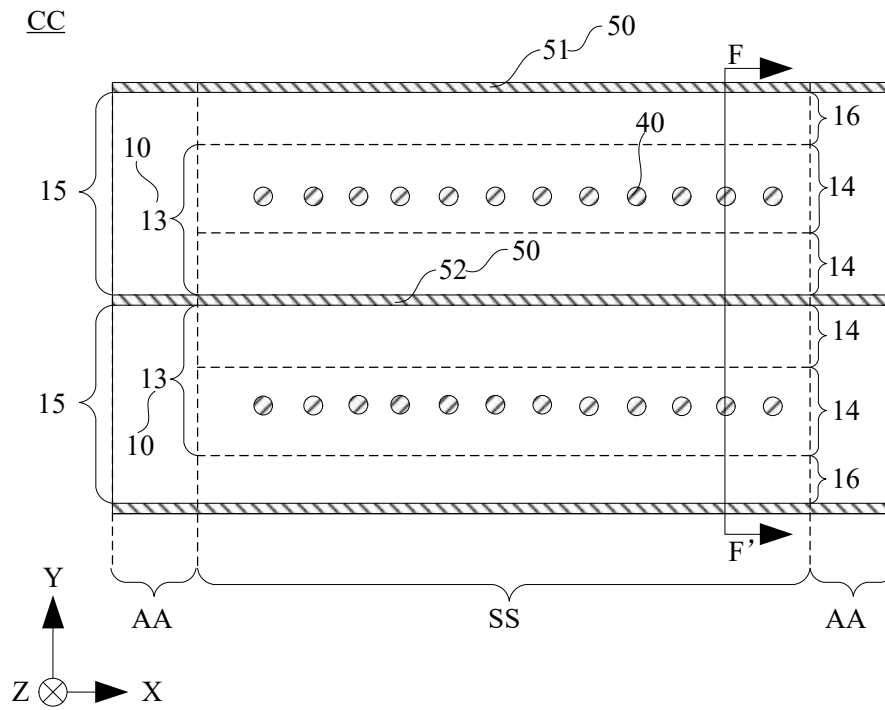


Fig. 10

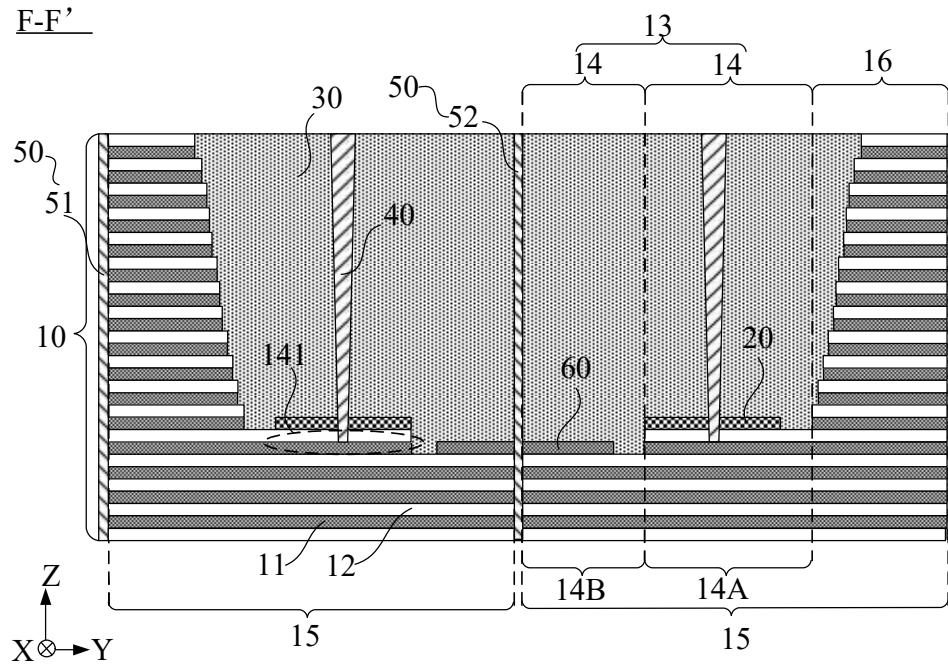


Fig. 11

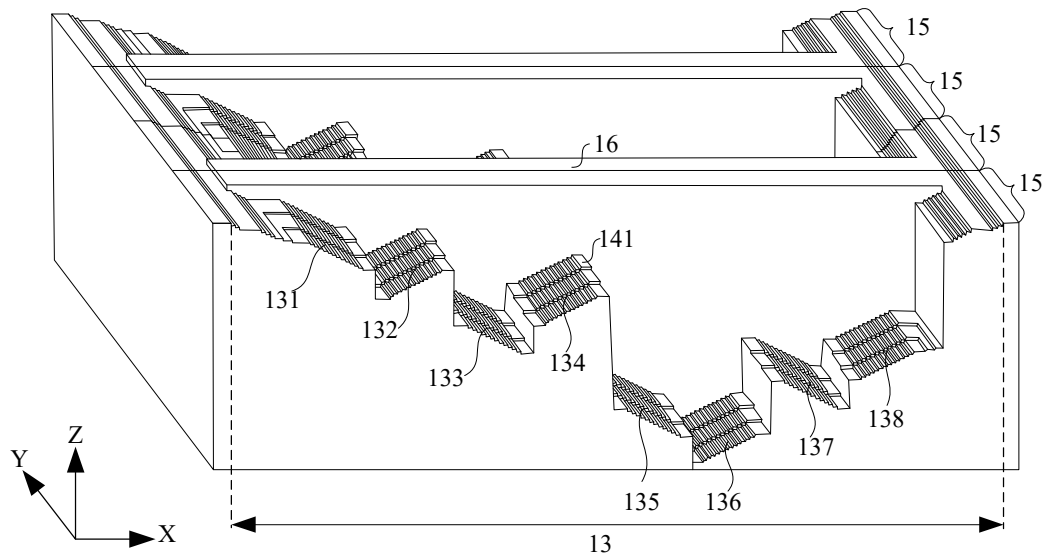


Fig. 12A

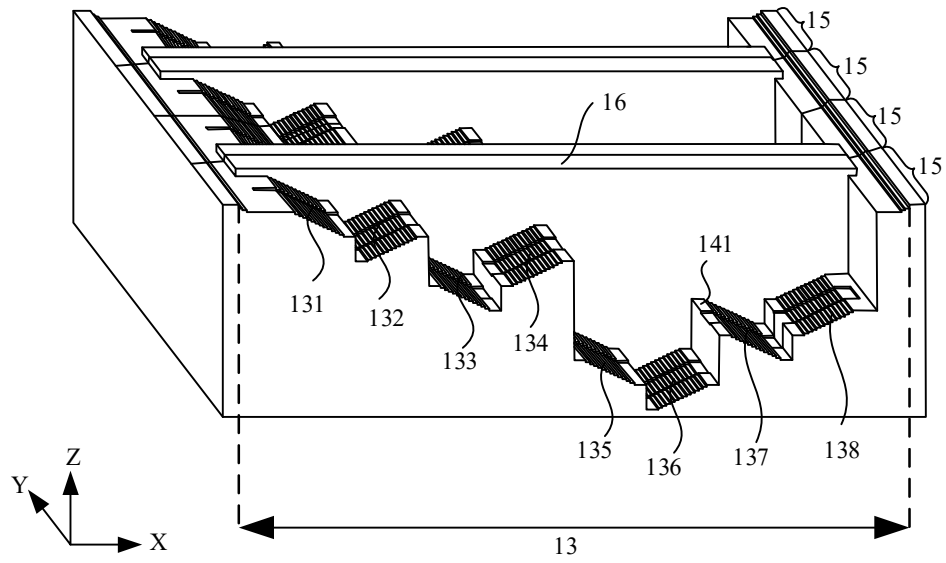


Fig. 12B

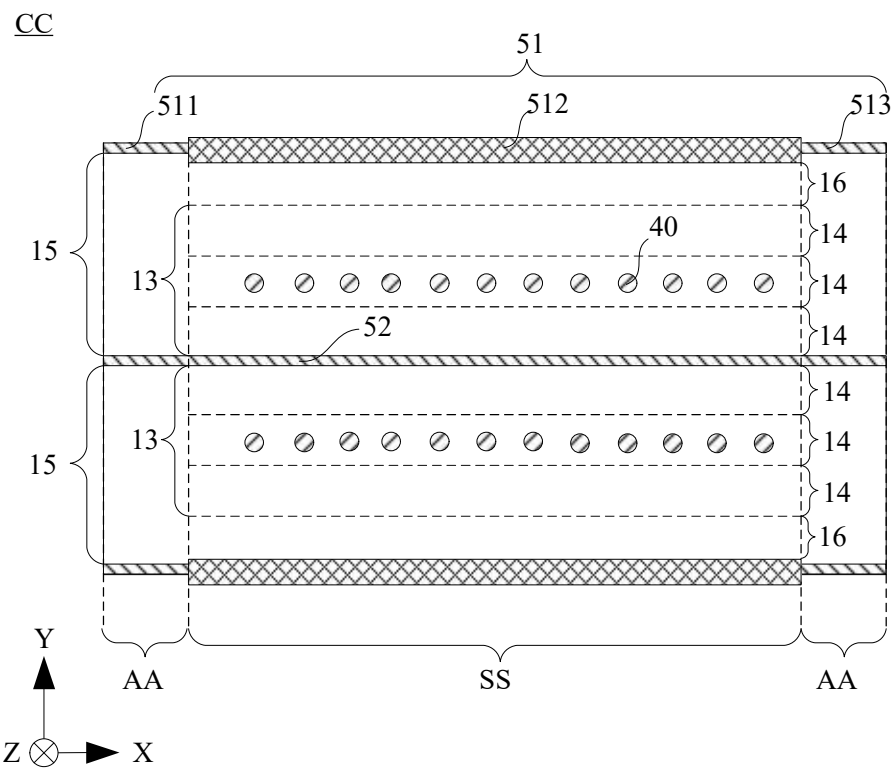


Fig. 13

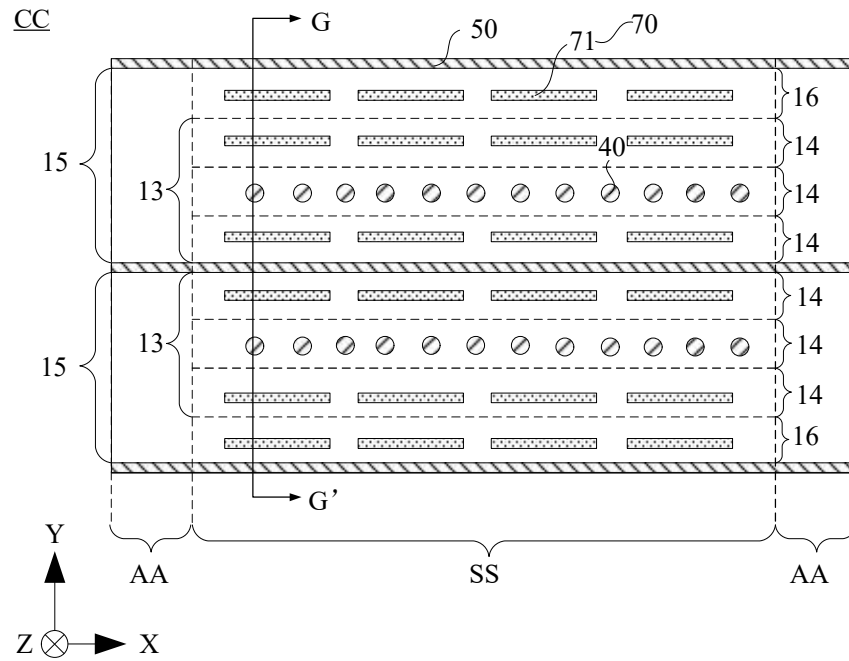


Fig. 14

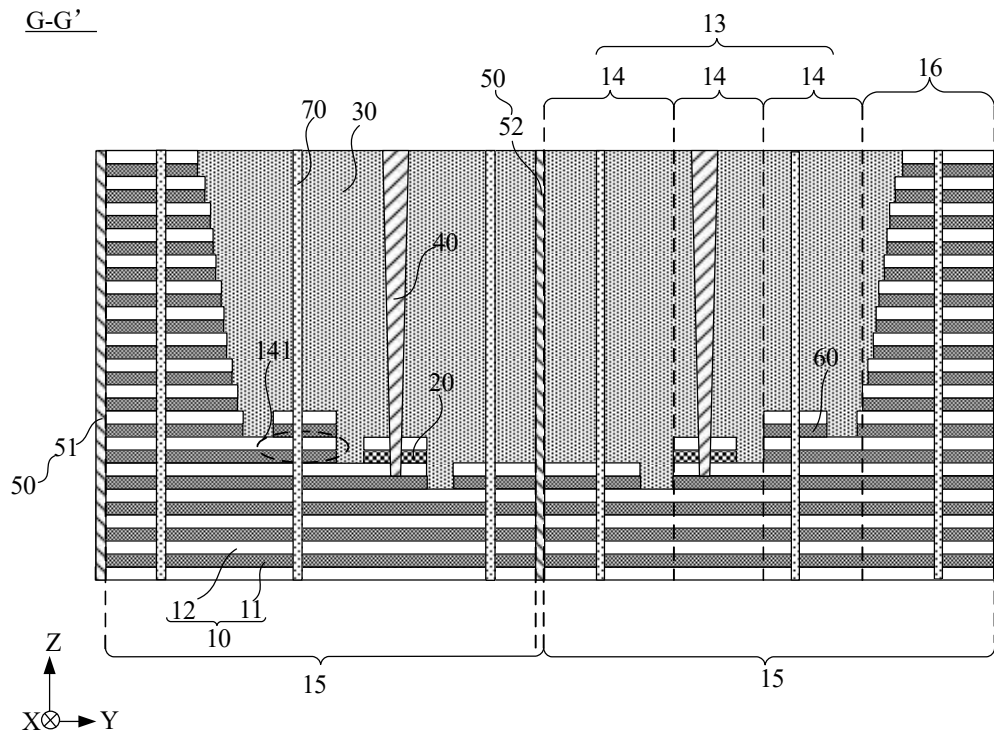


Fig. 15

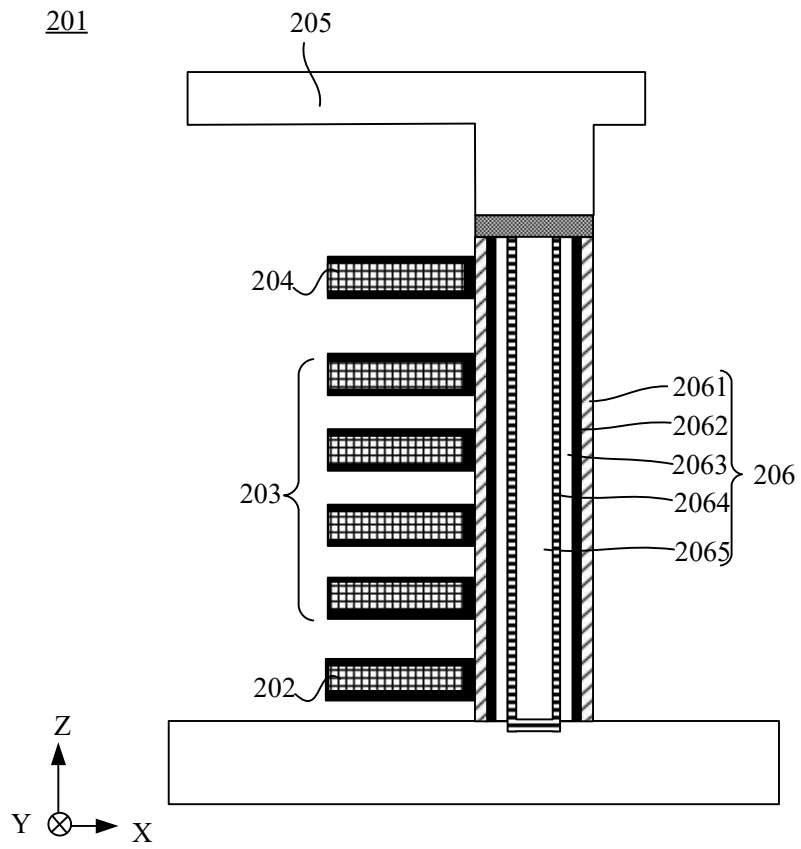


Fig. 16

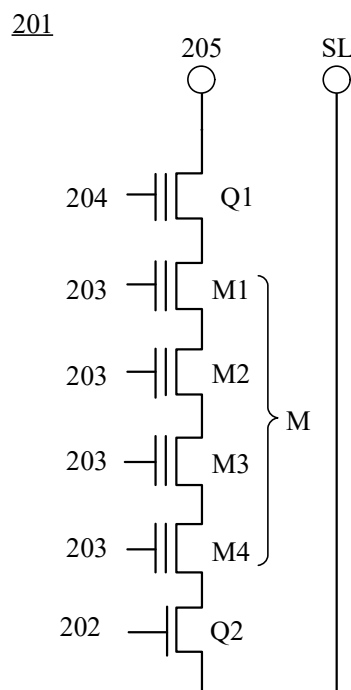


Fig. 17

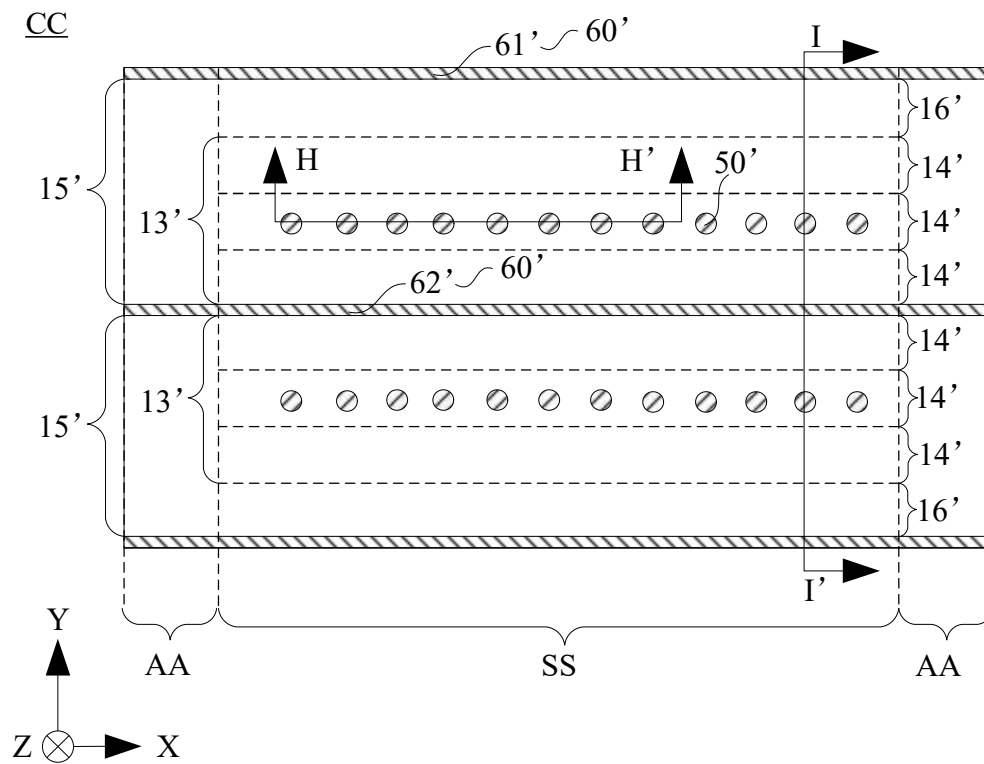


Fig. 18

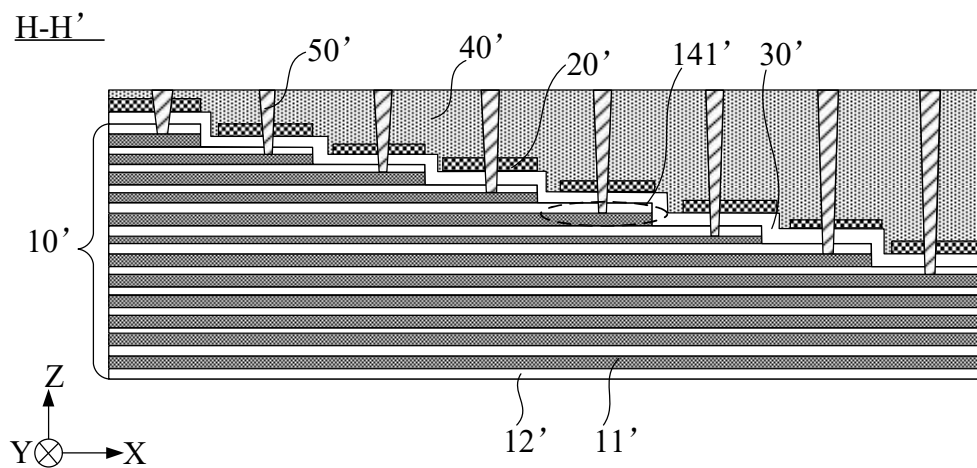


Fig. 19A

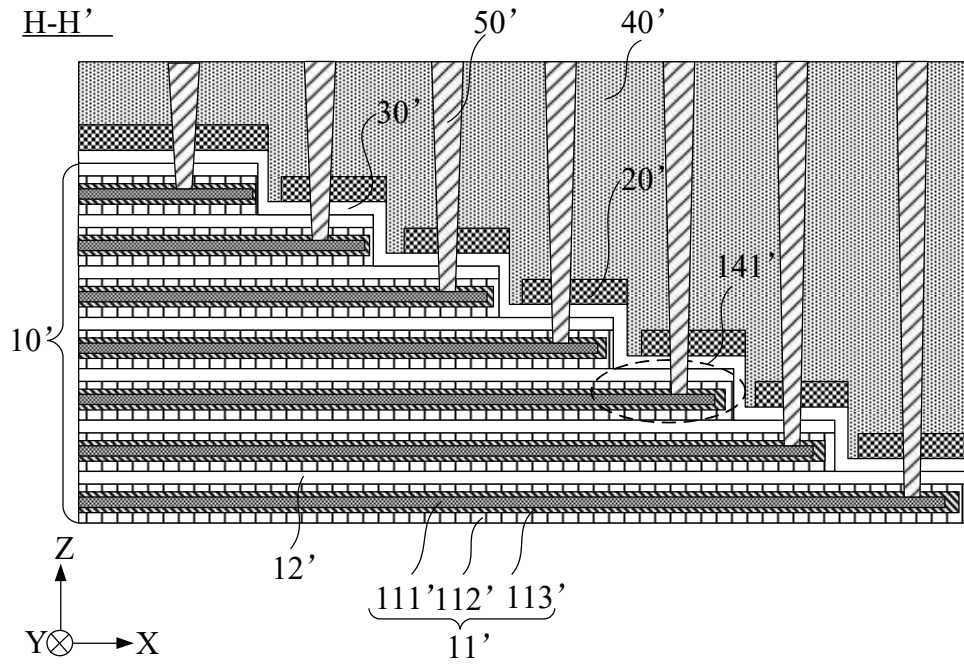


Fig. 19B

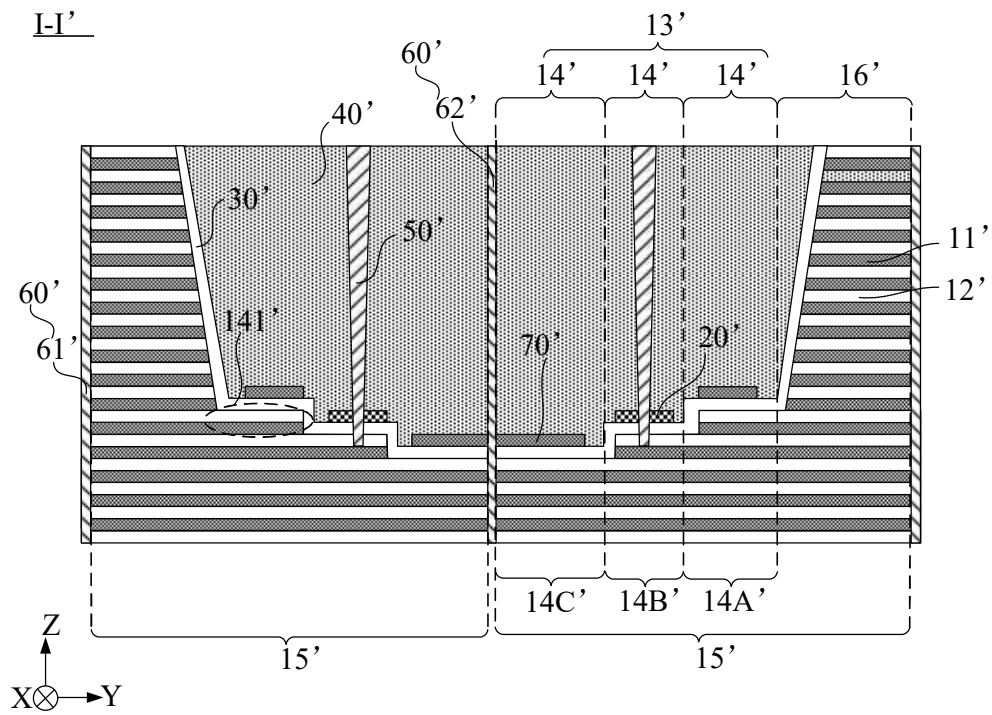


Fig. 20

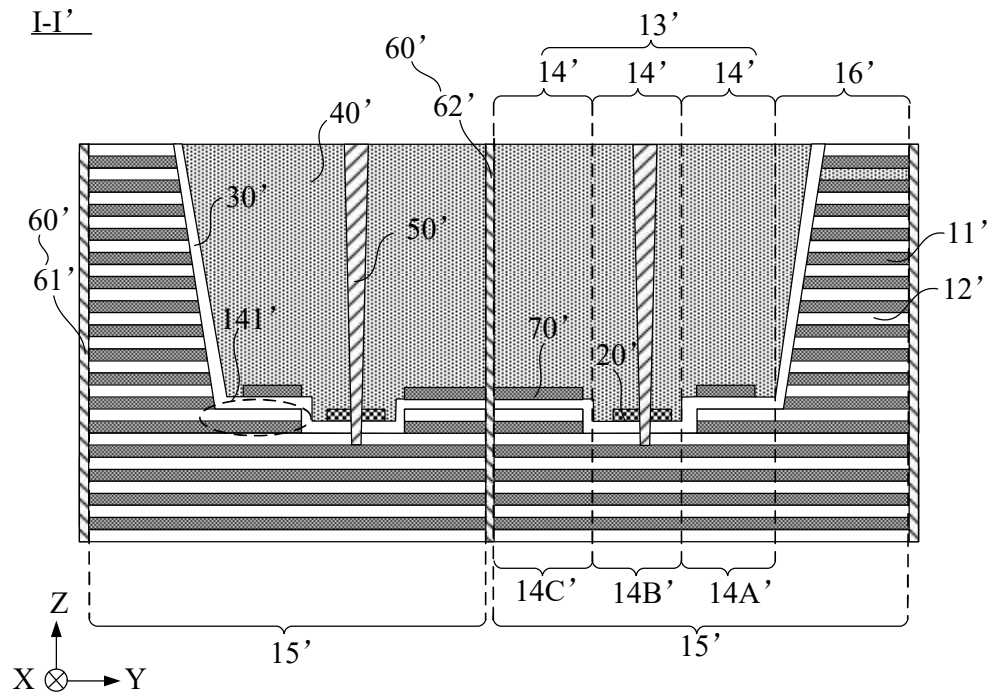


Fig. 21

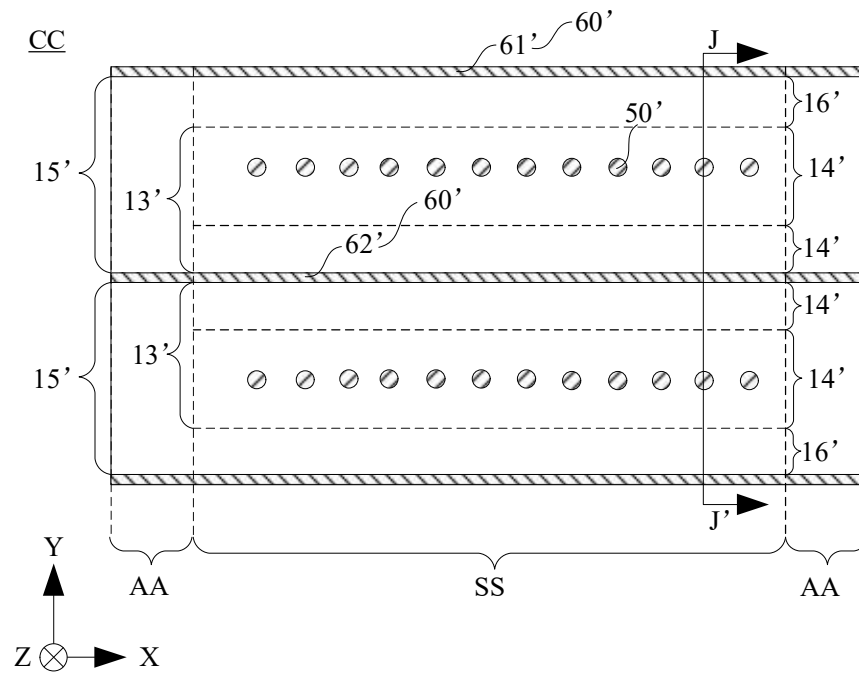


Fig. 22

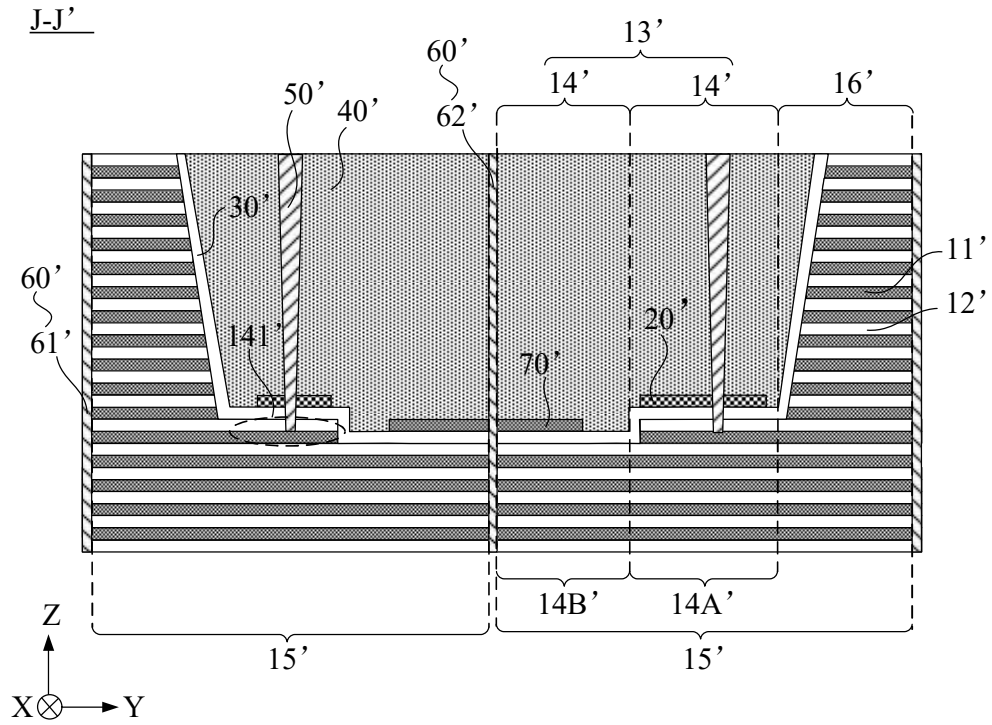


Fig. 23

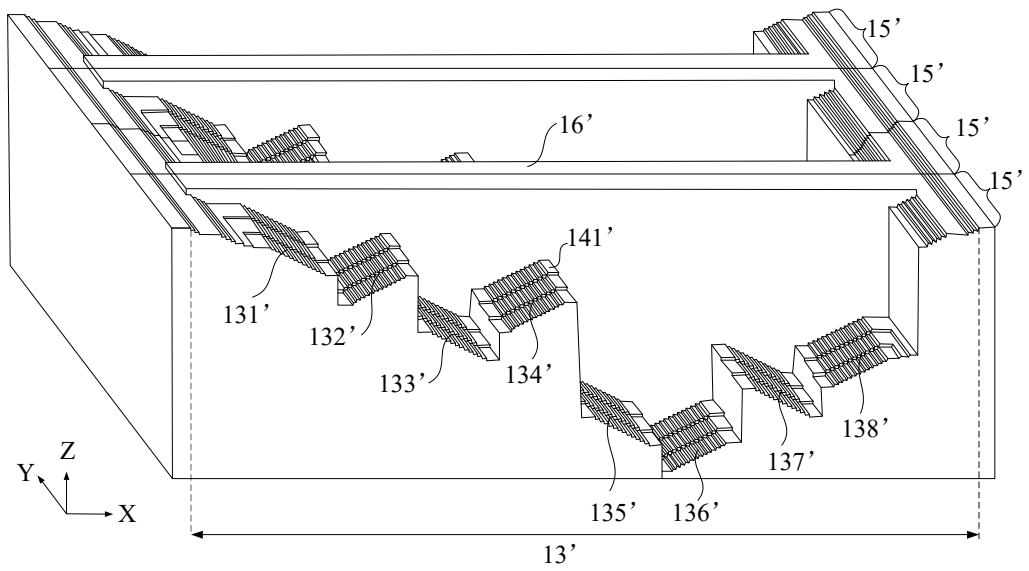


Fig. 24A

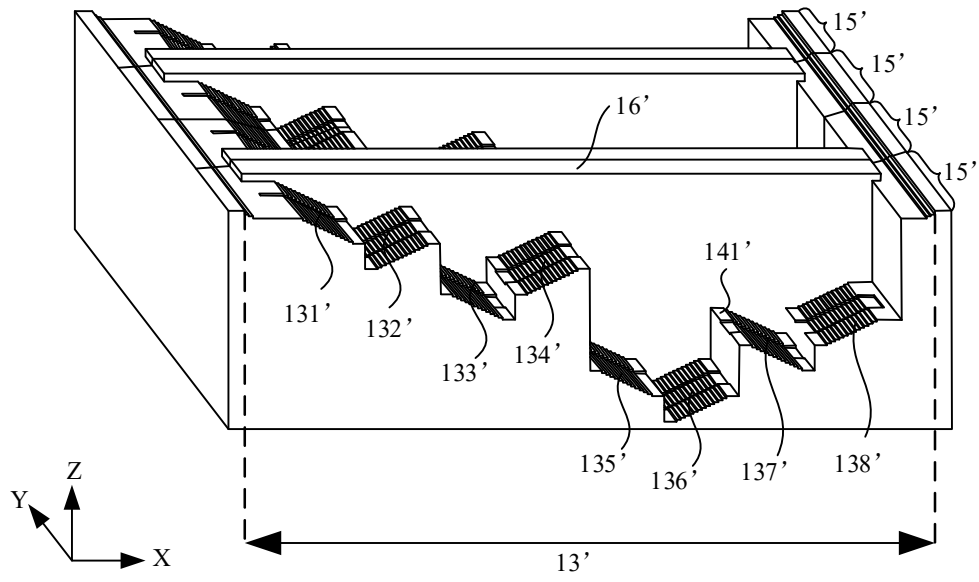


Fig. 24B

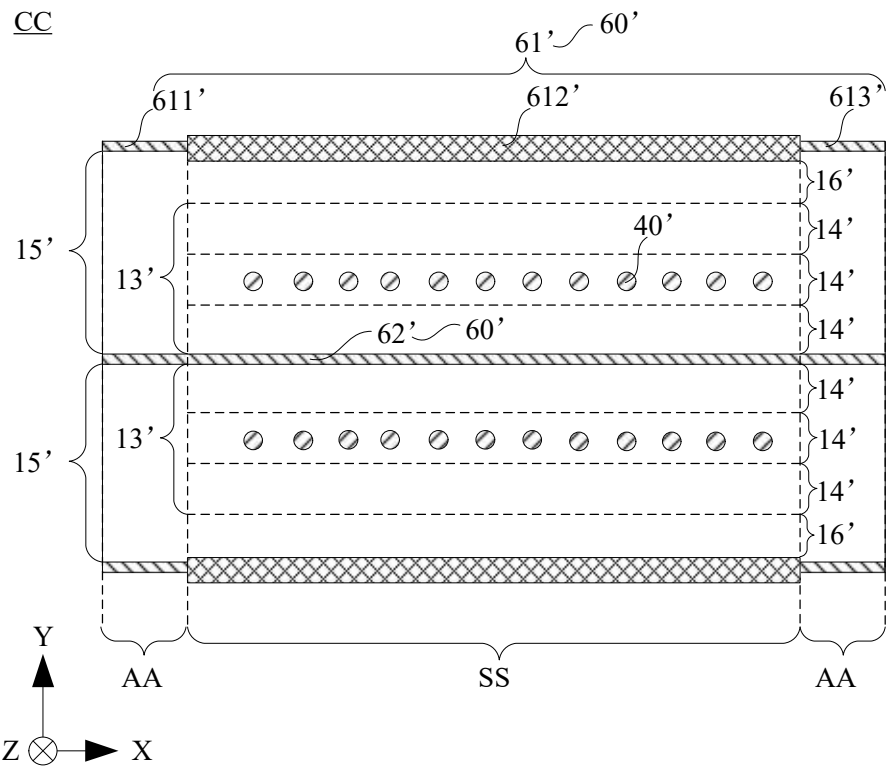


Fig. 25

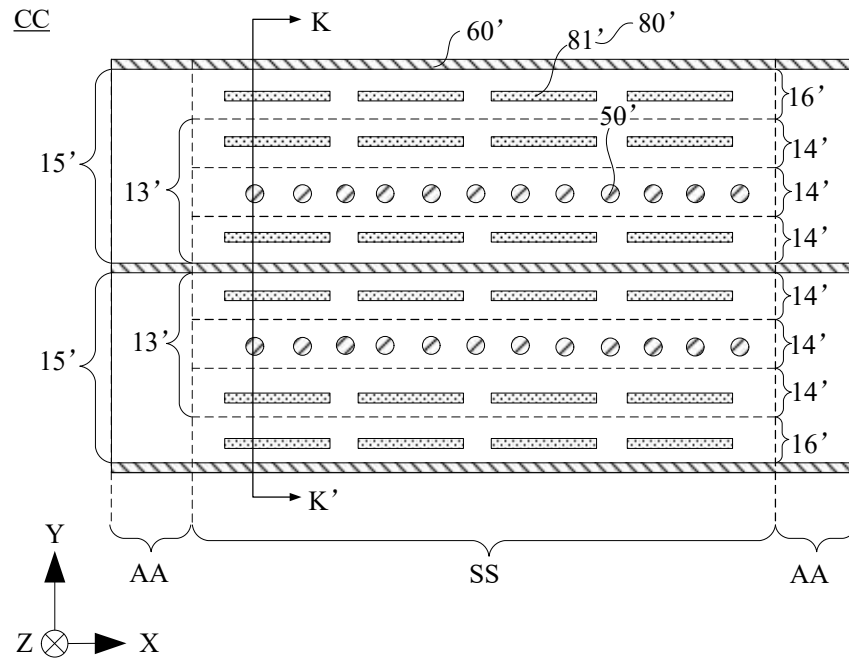


Fig. 26

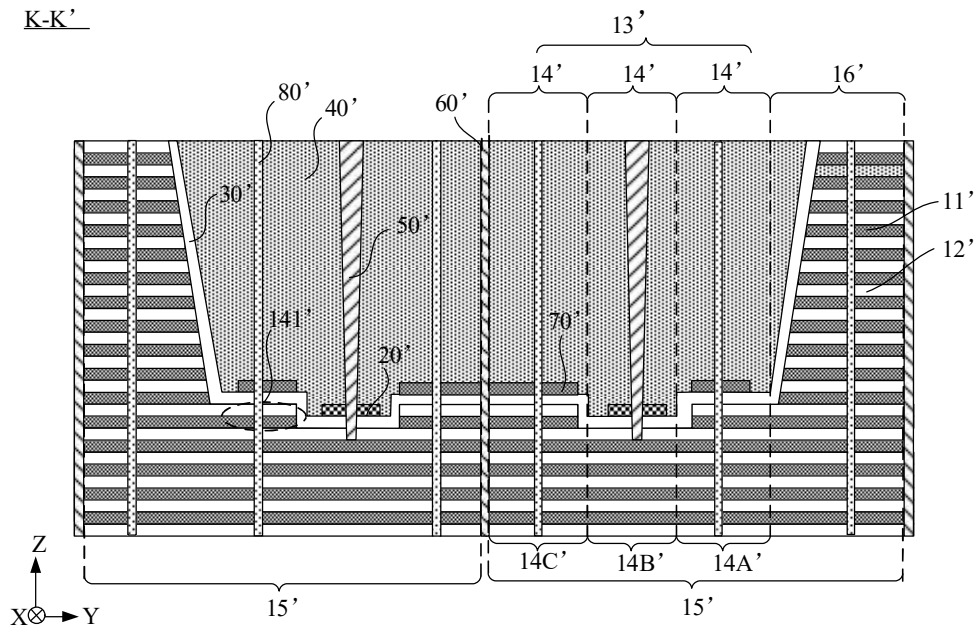


Fig. 27

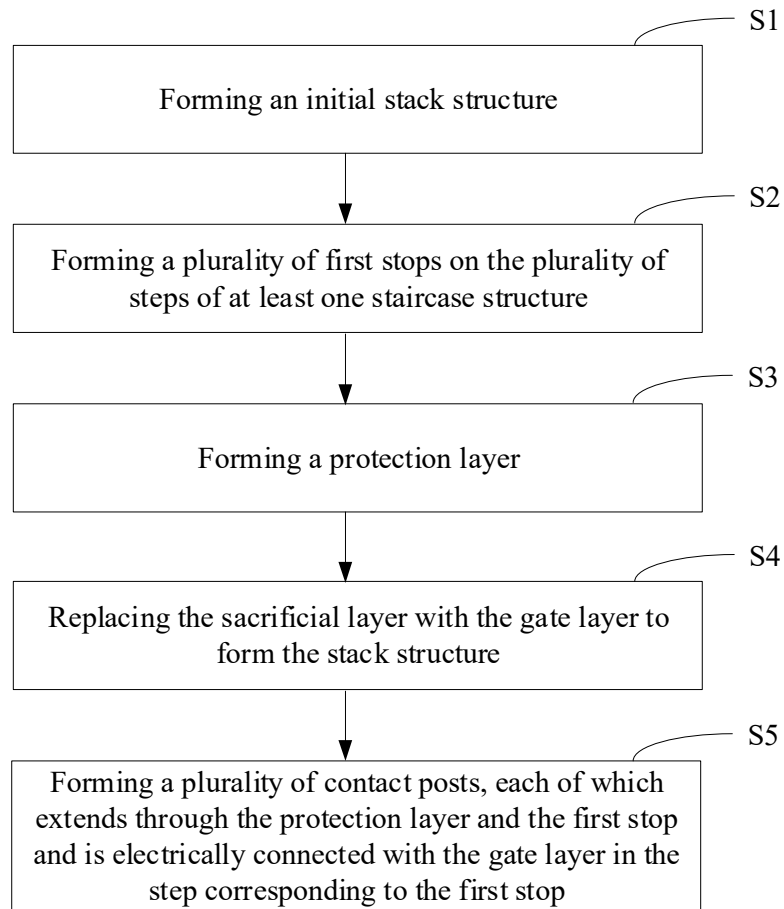


Fig. 28

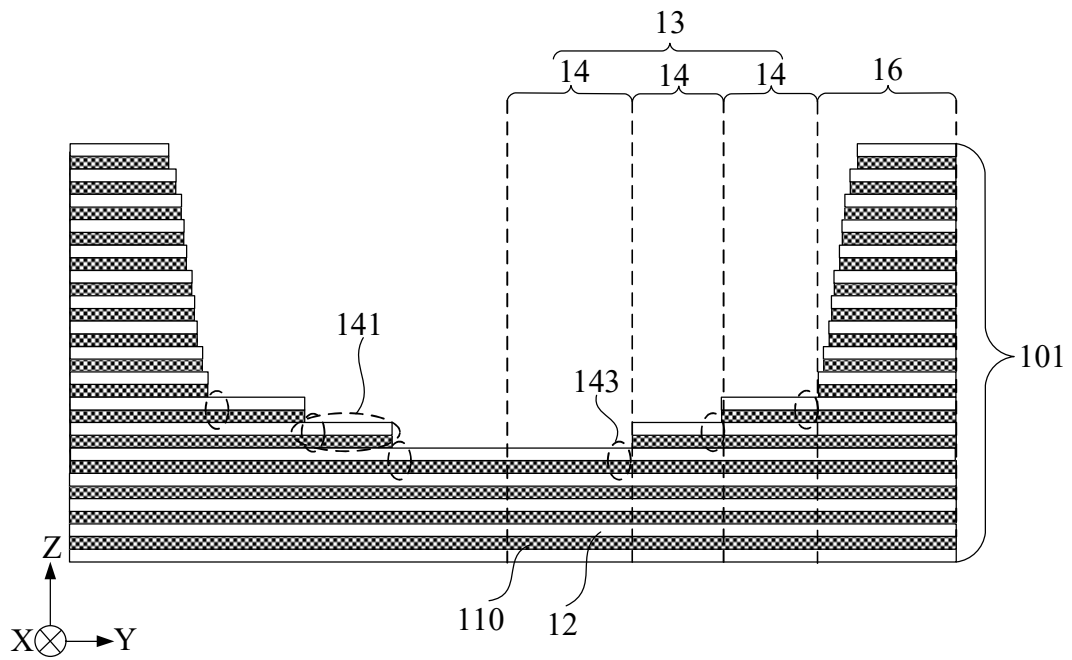


Fig. 29A

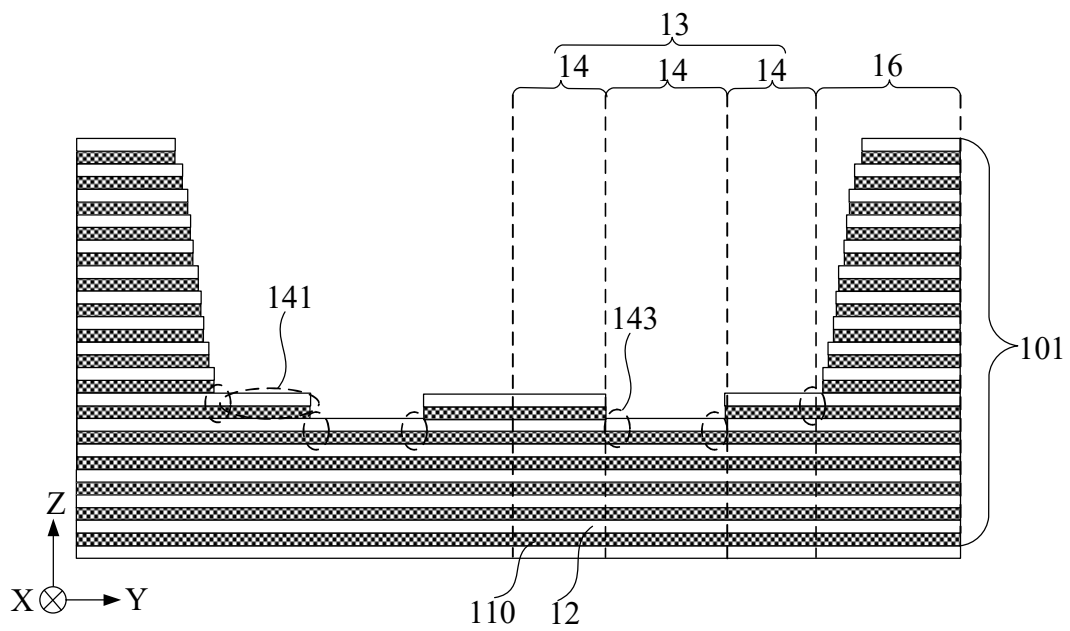


Fig. 29B

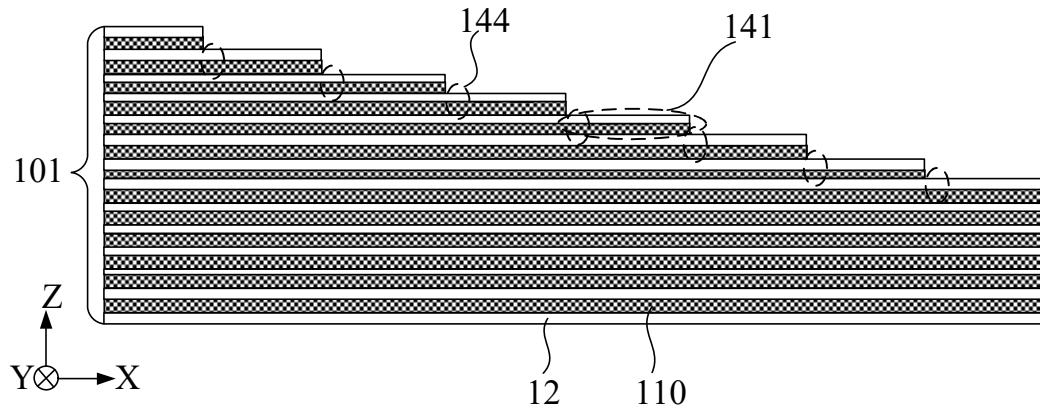


Fig. 30

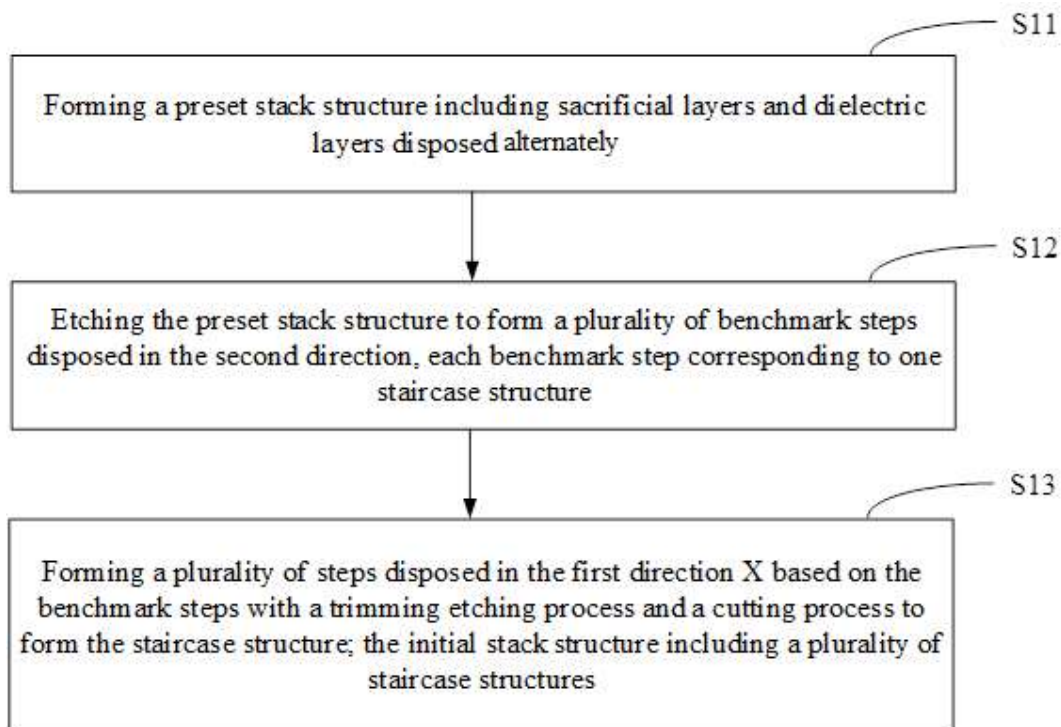


Fig. 31

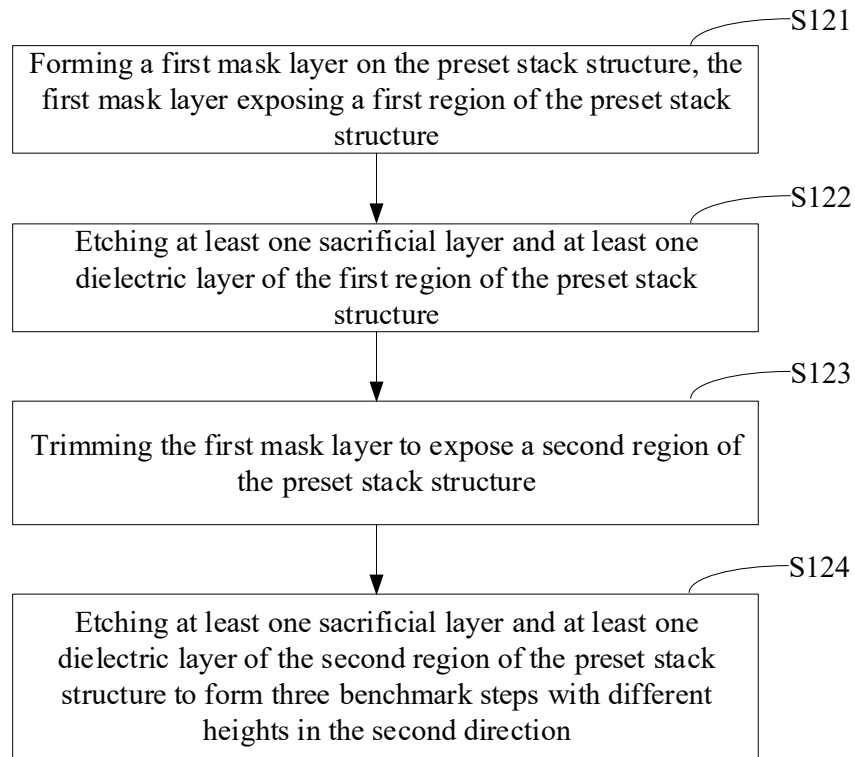


Fig. 32

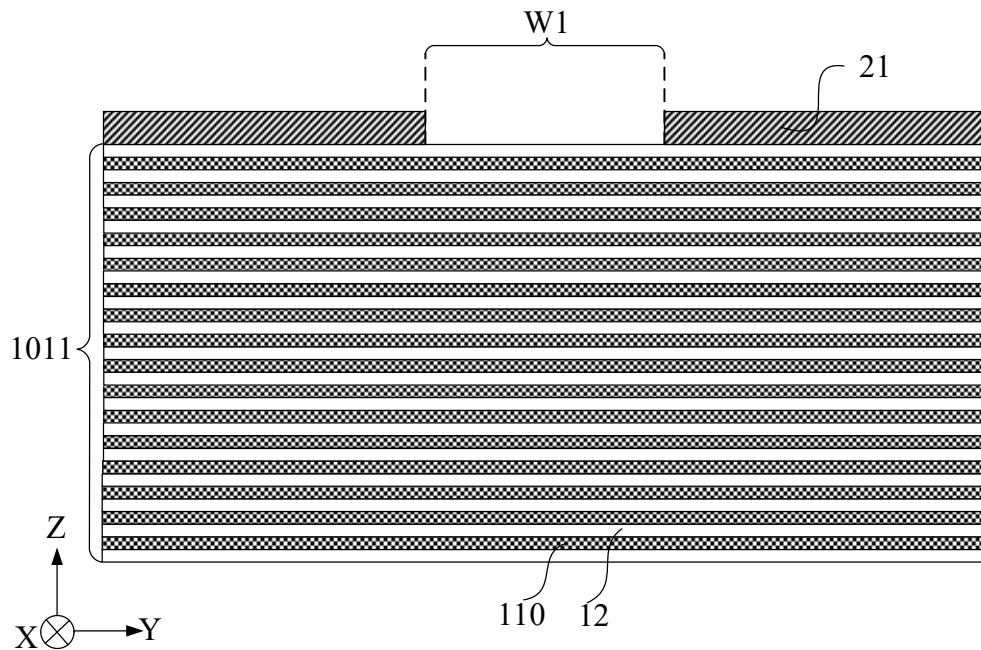


Fig. 33A

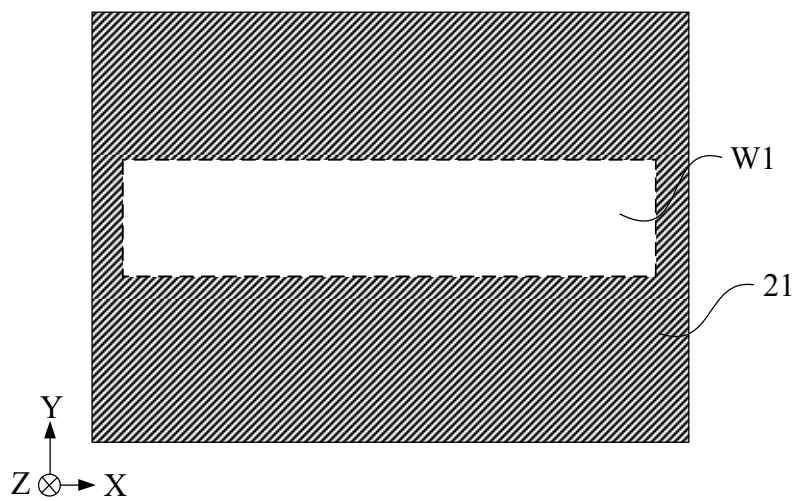


Fig. 33B

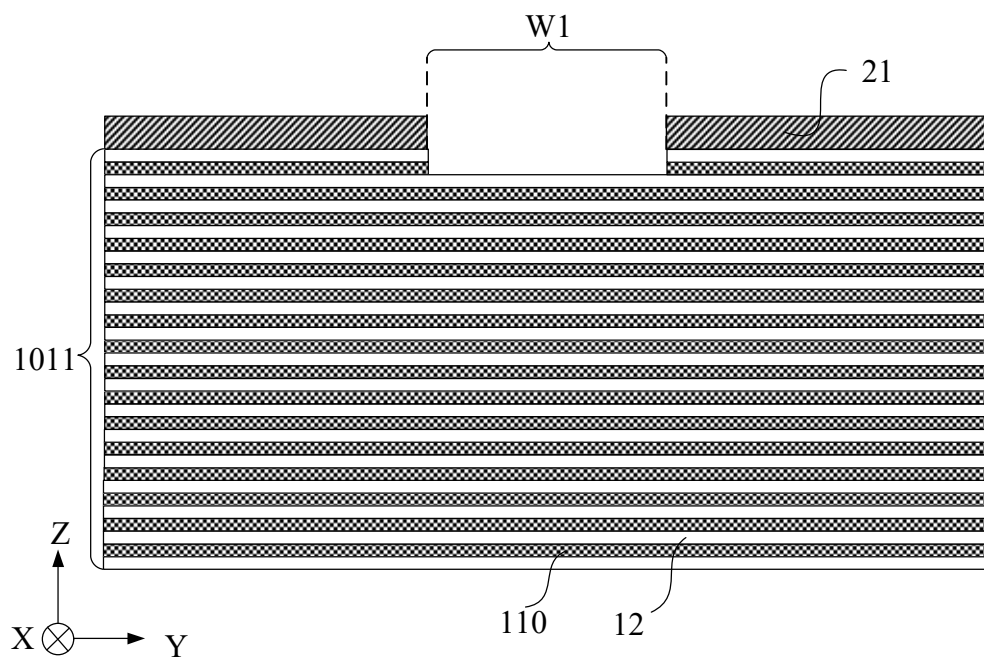


Fig. 34

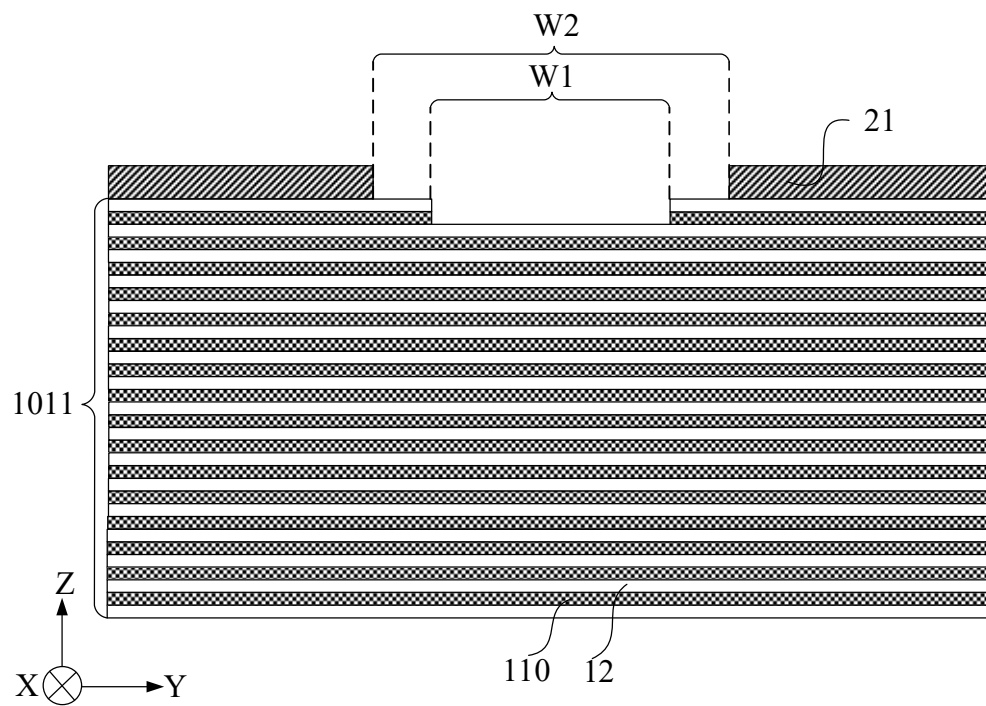


Fig. 35A

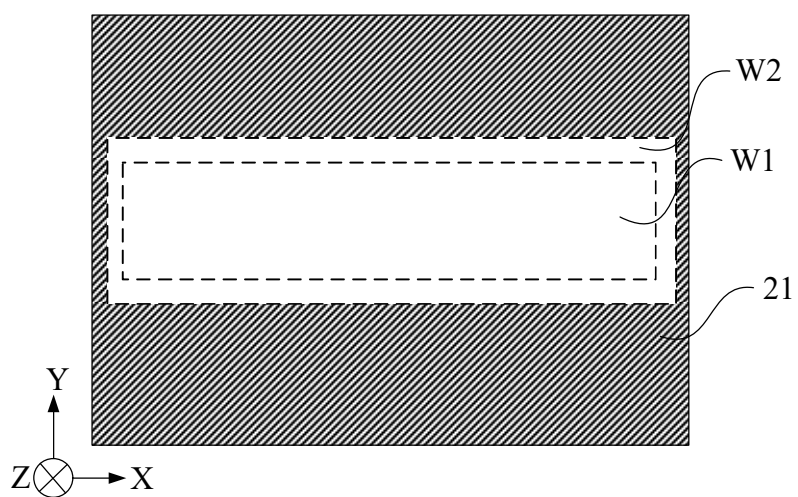


Fig. 35B

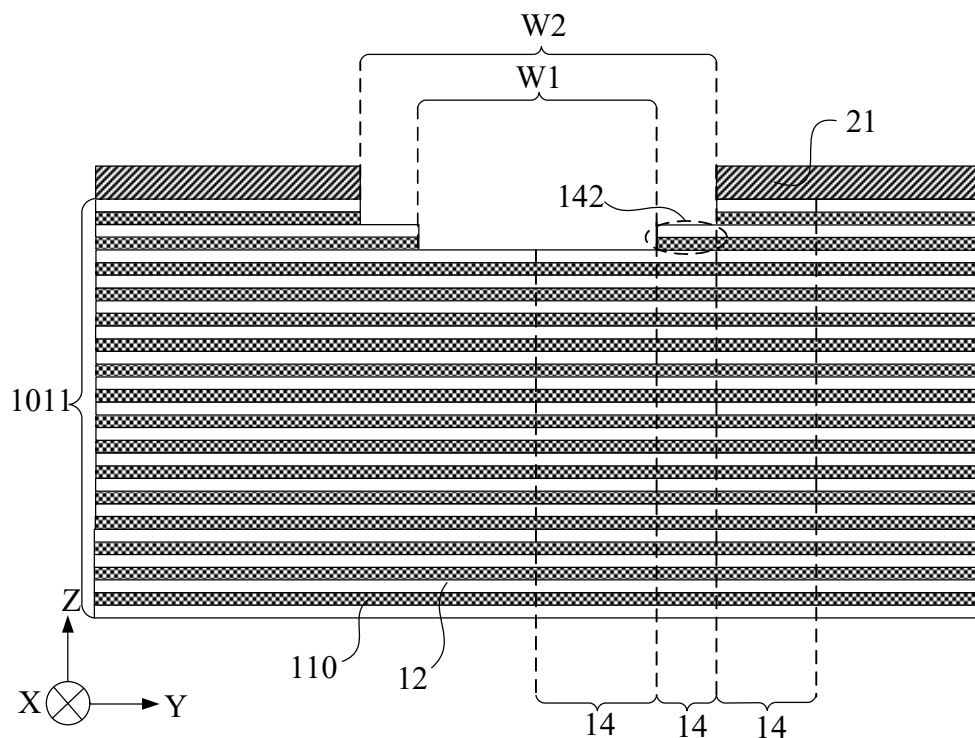


Fig. 36

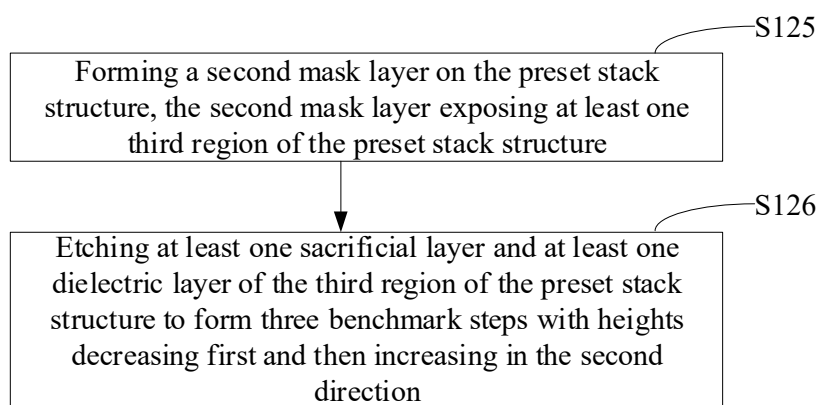


Fig. 37

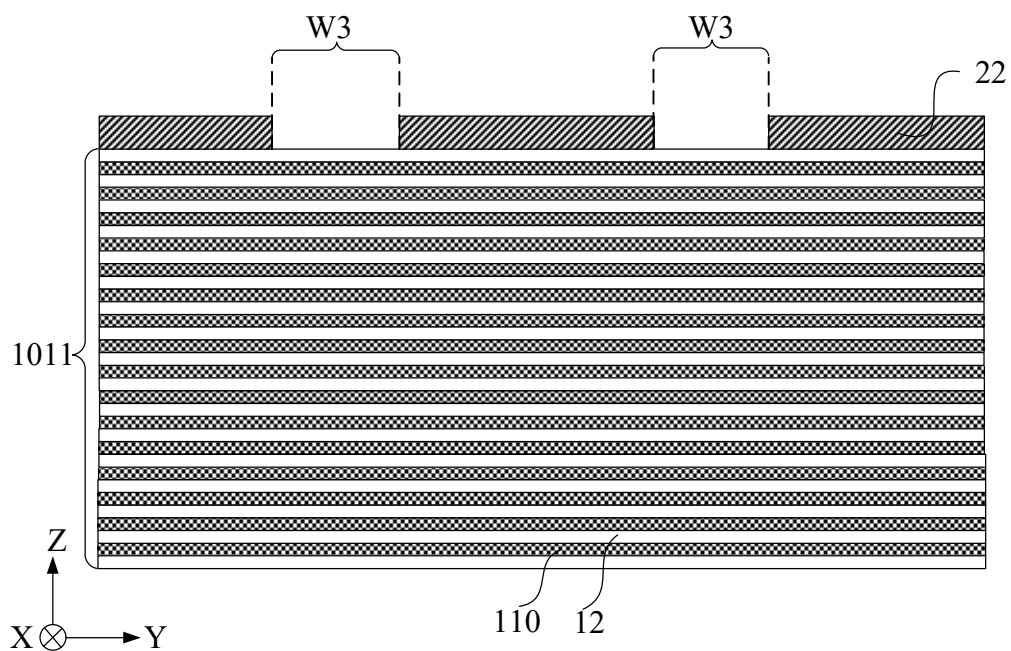


Fig. 38

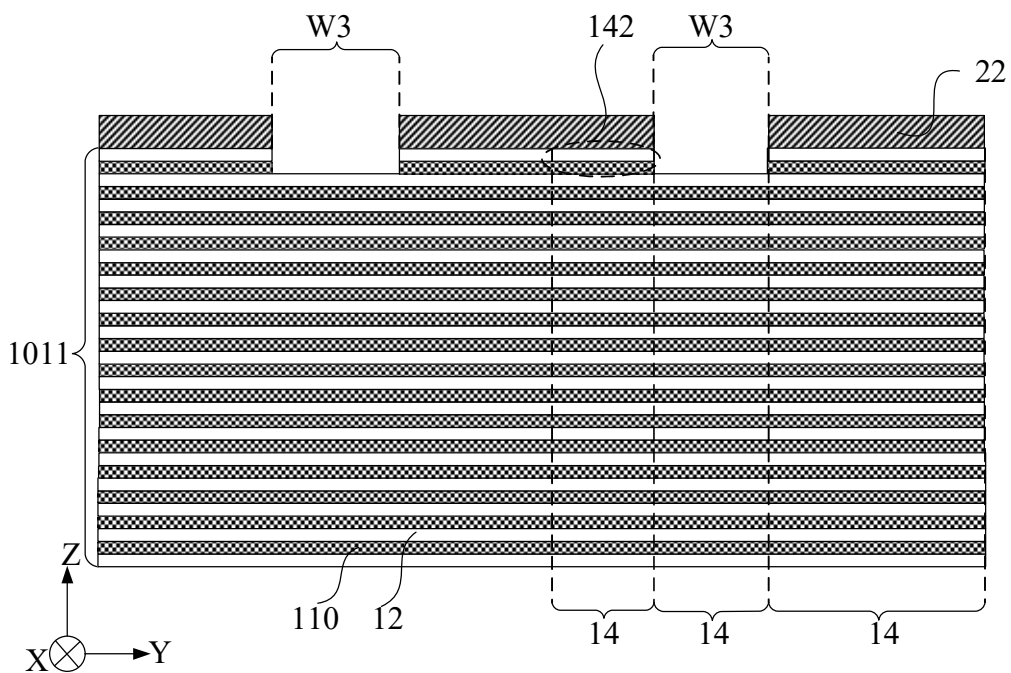


Fig. 39

S21

Etching the uppermost sacrificial layer and dielectric layer of each step to form a plurality of first stops

Fig. 40

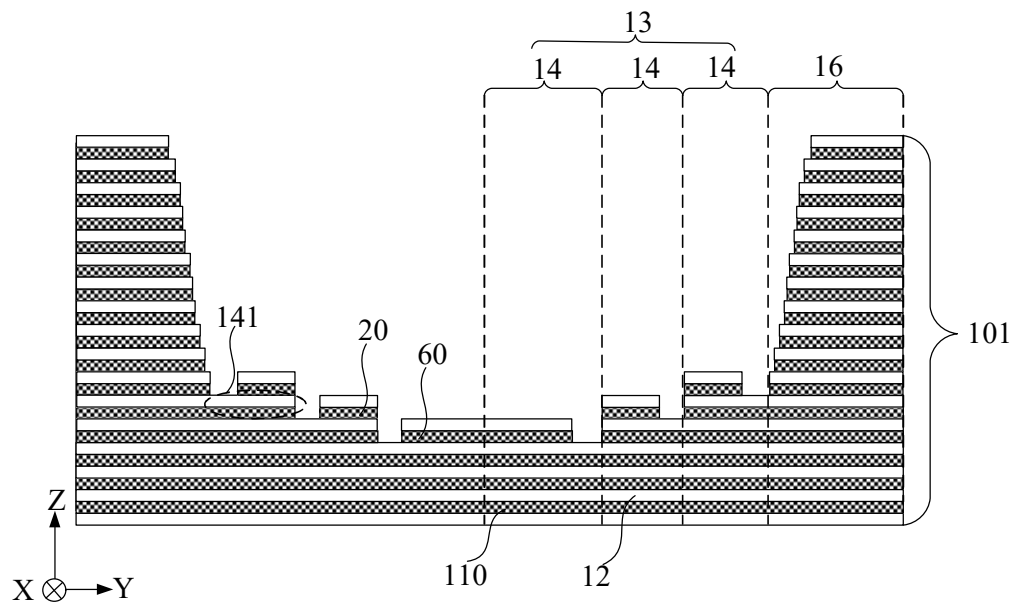


Fig. 41A

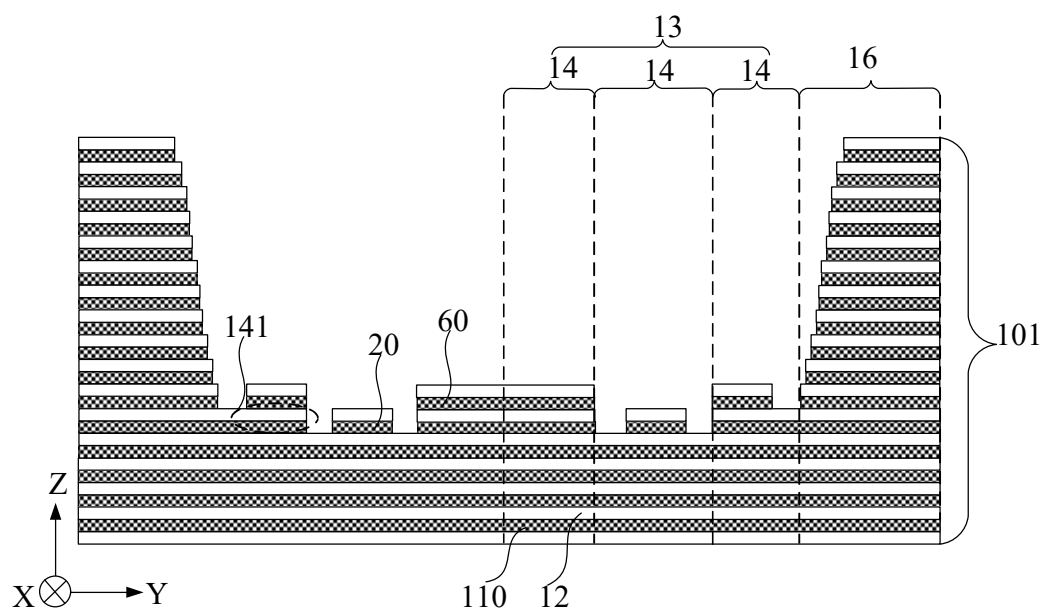


Fig. 41B

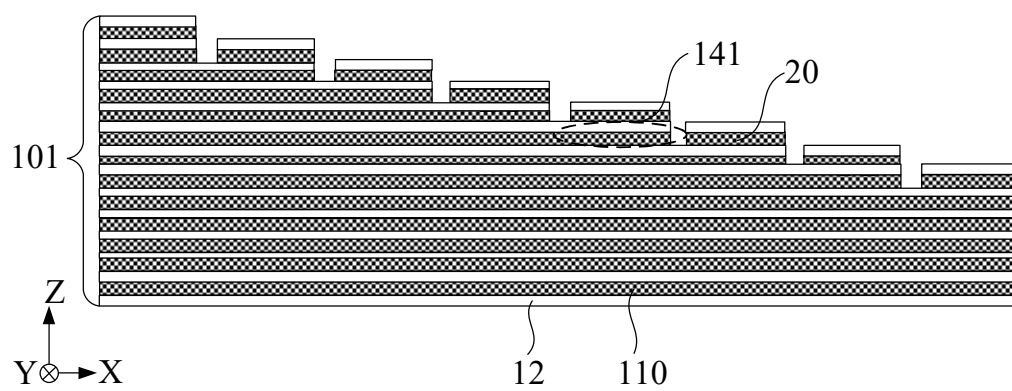


Fig. 42

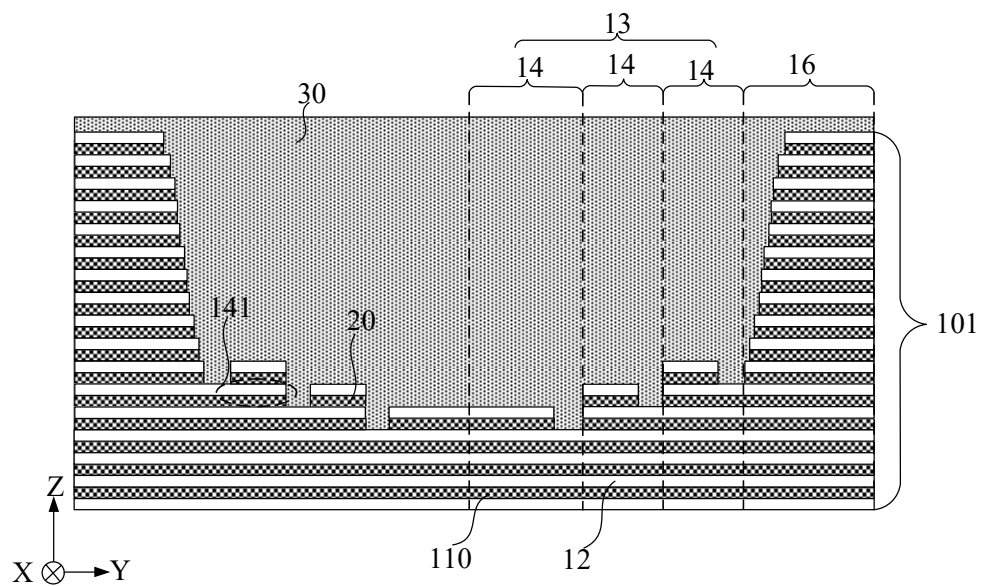


Fig. 43

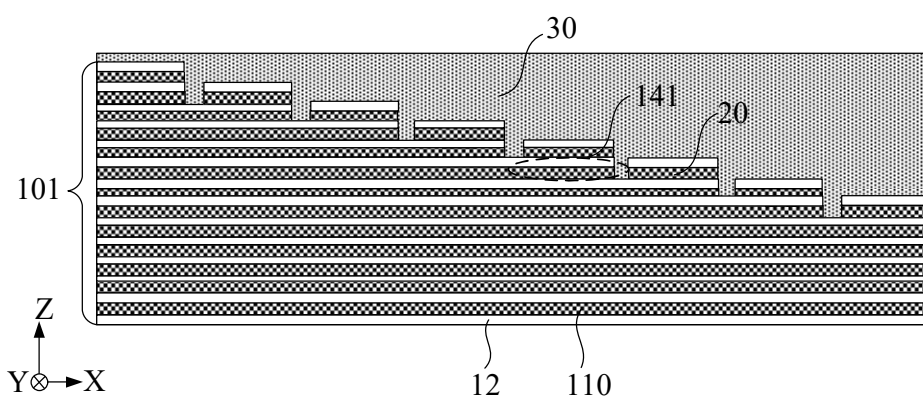


Fig. 44

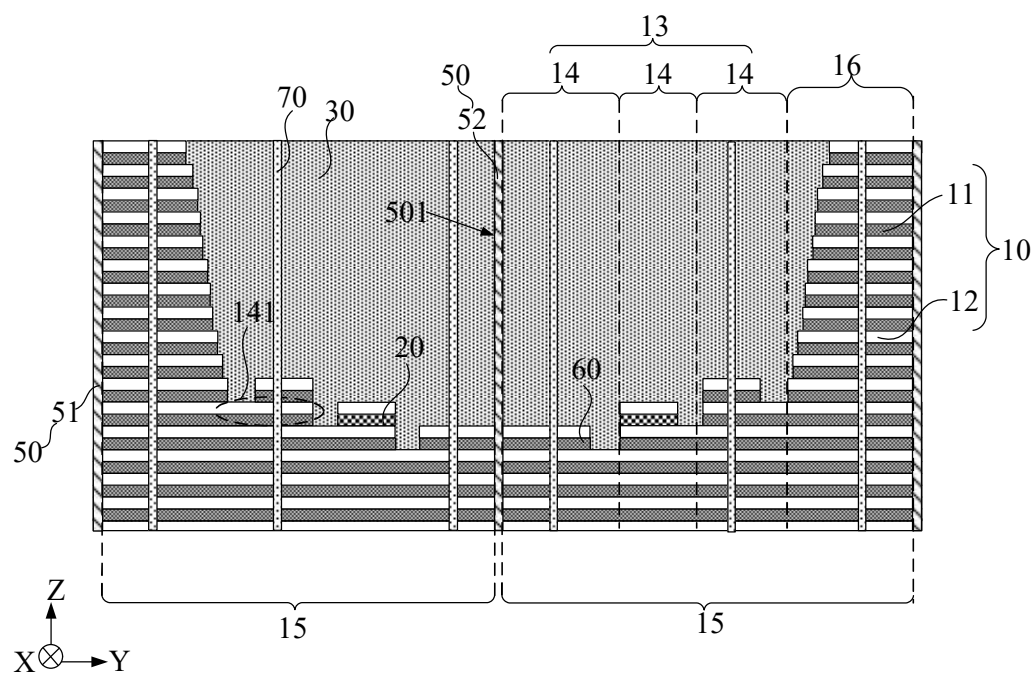


Fig. 45

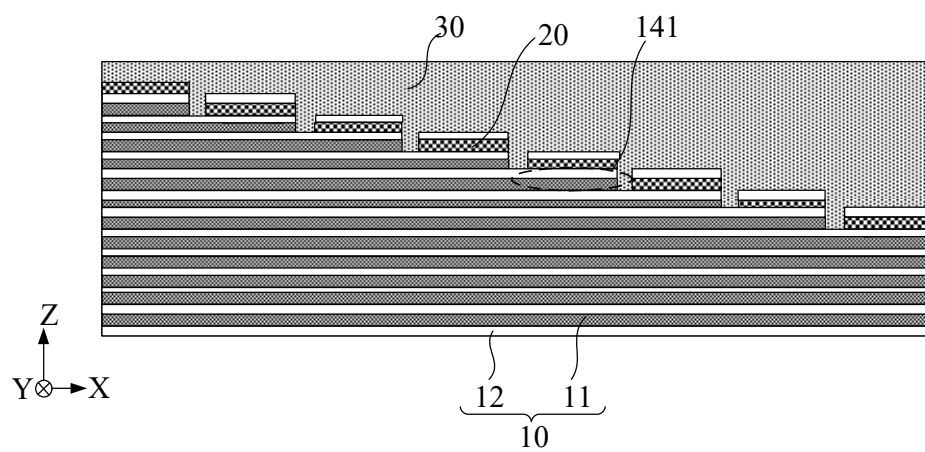


Fig. 46

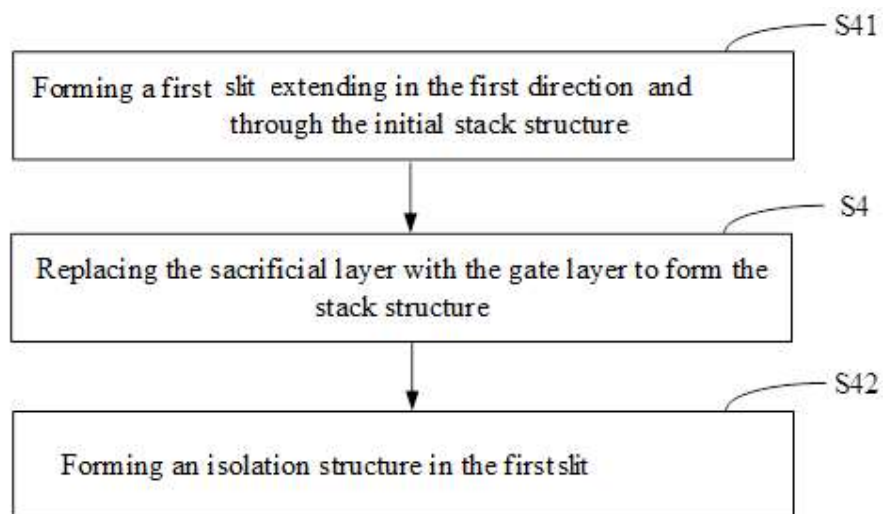


Fig. 47

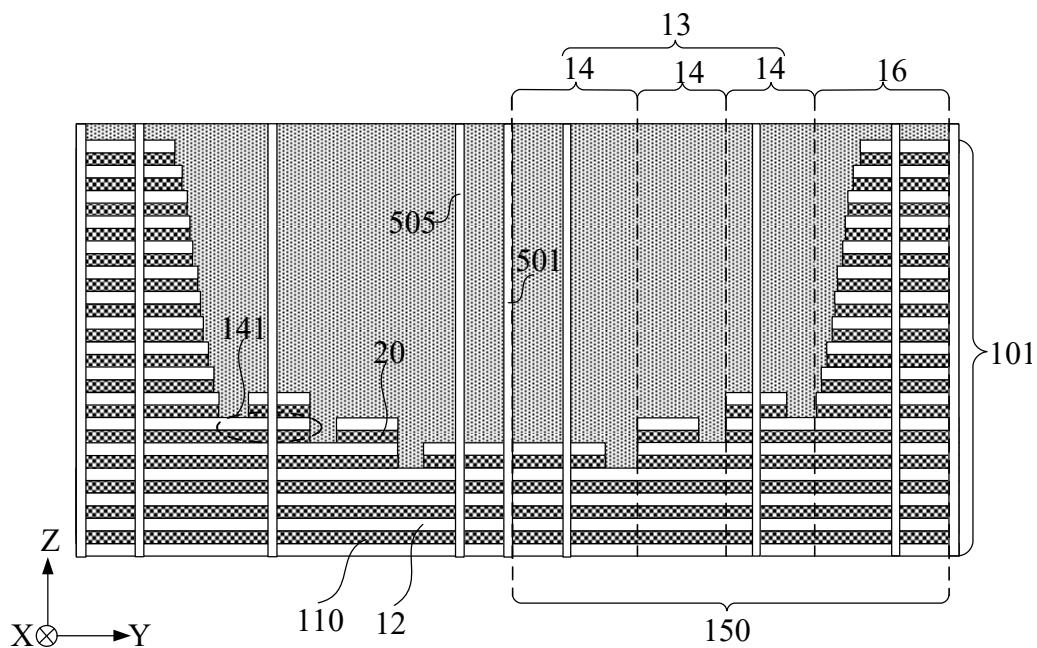


Fig. 48

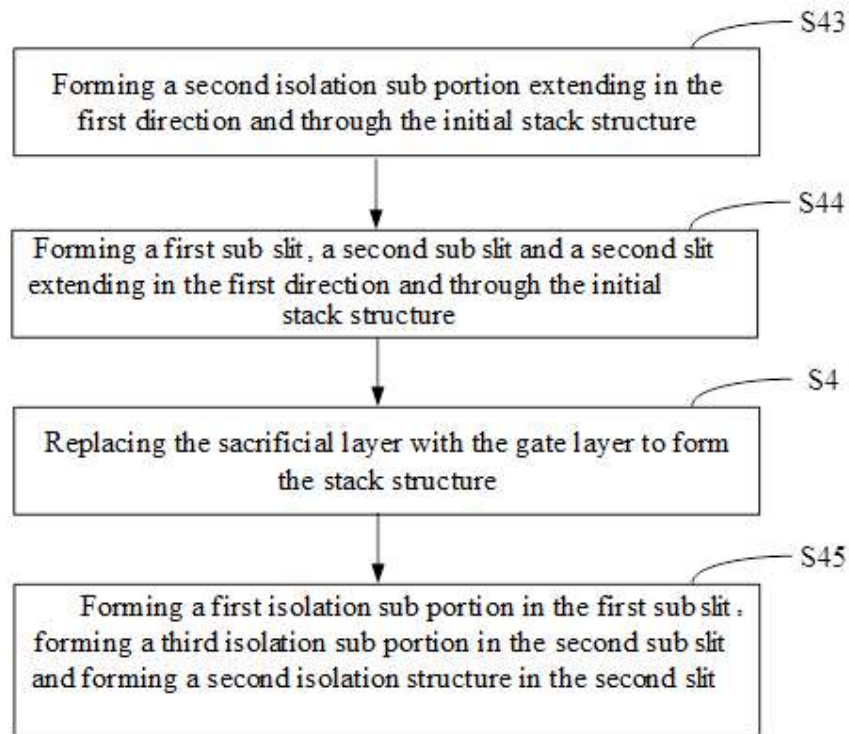


Fig. 49

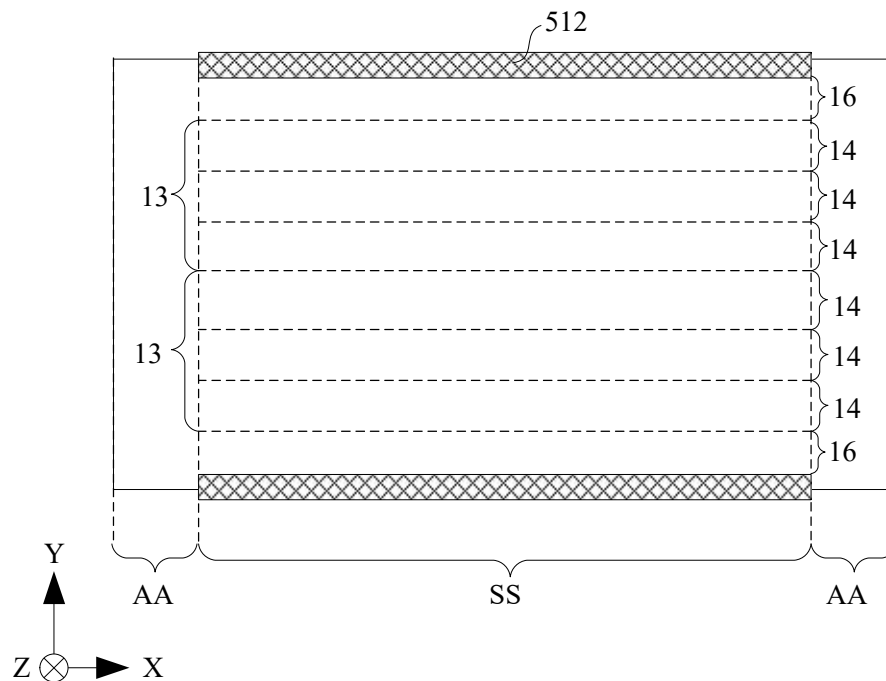


Fig. 50

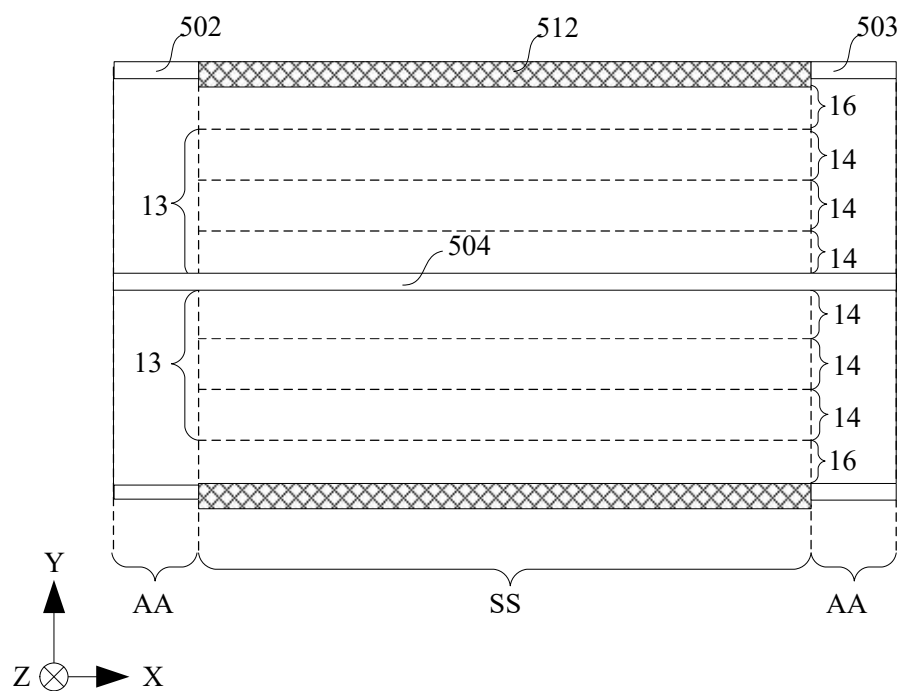


Fig. 51

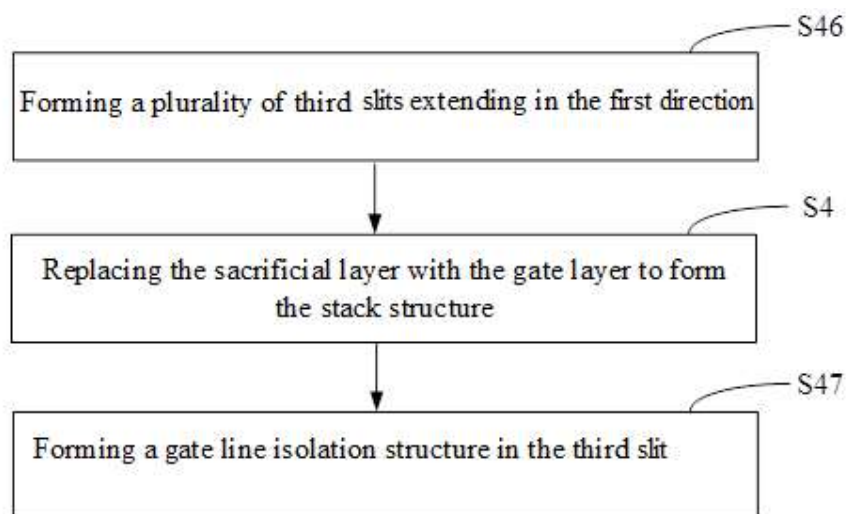


Fig. 52

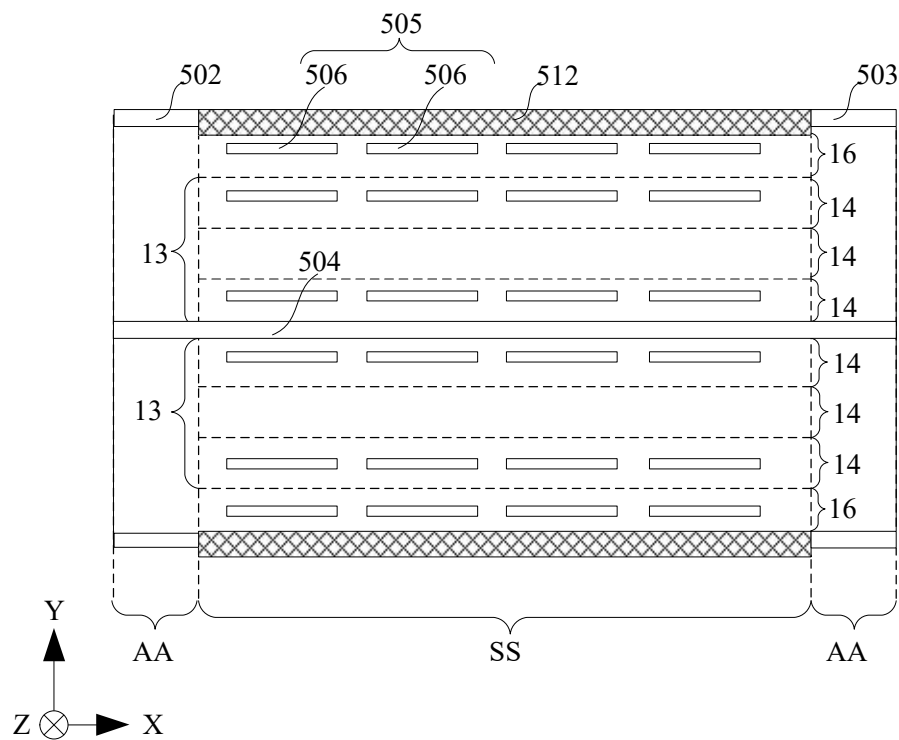


Fig. 53

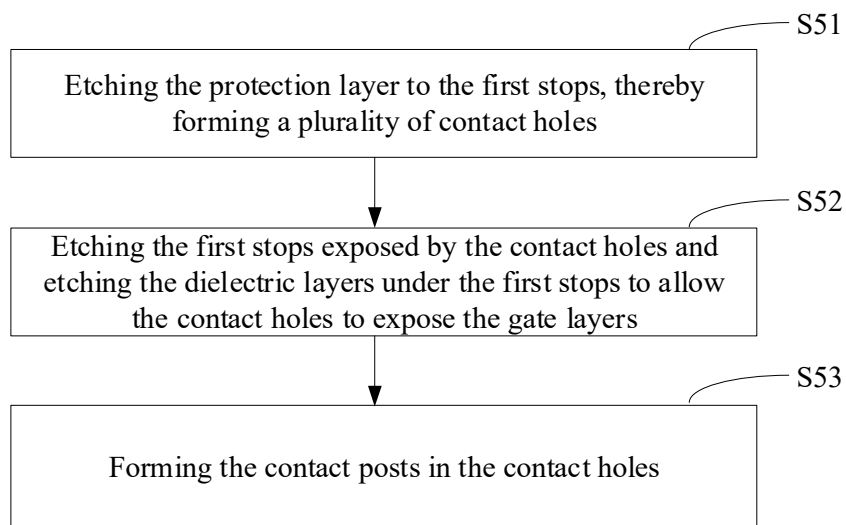


Fig. 54

A cross-sectional view of a semiconductor device. The device consists of a substrate 11, a base layer 12, and a stack of layers 10. The stack of layers 10 includes a layer 20 with openings 30 and 41, and a layer 141. A coordinate system (X, Y, Z) is shown at the bottom left.

Fig. 56

Fig. 58

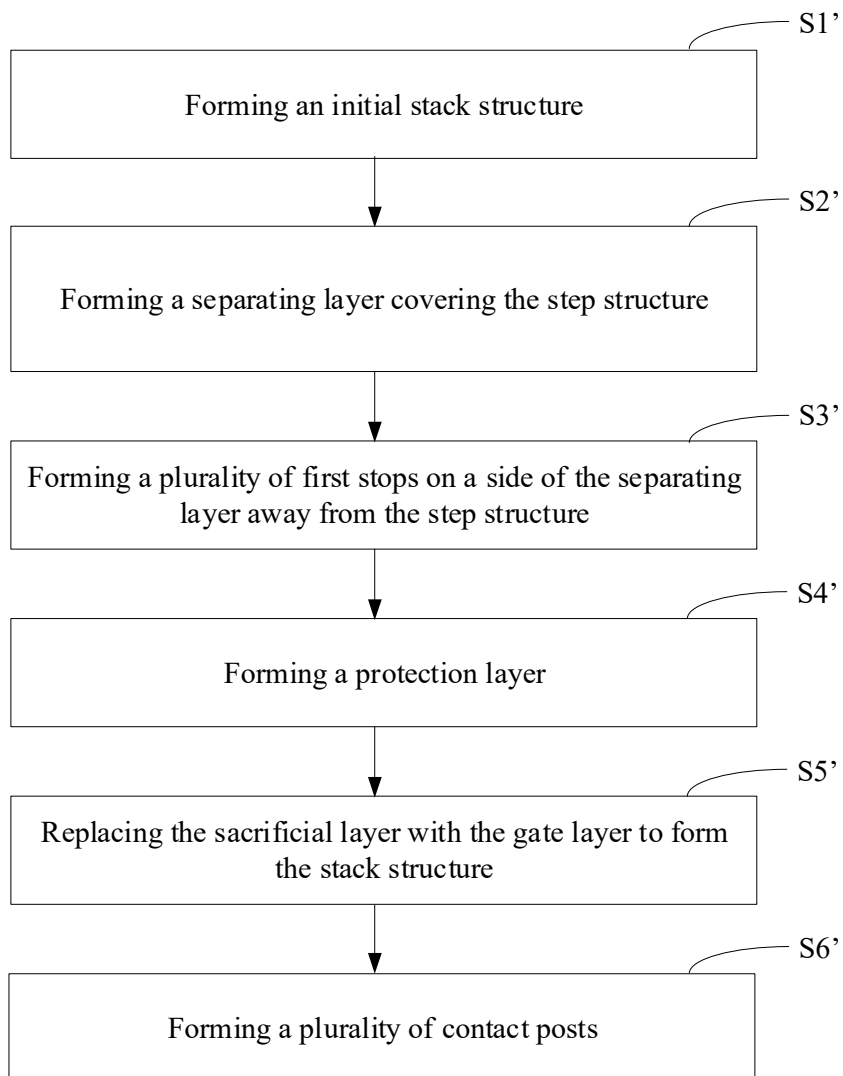


Fig. 59

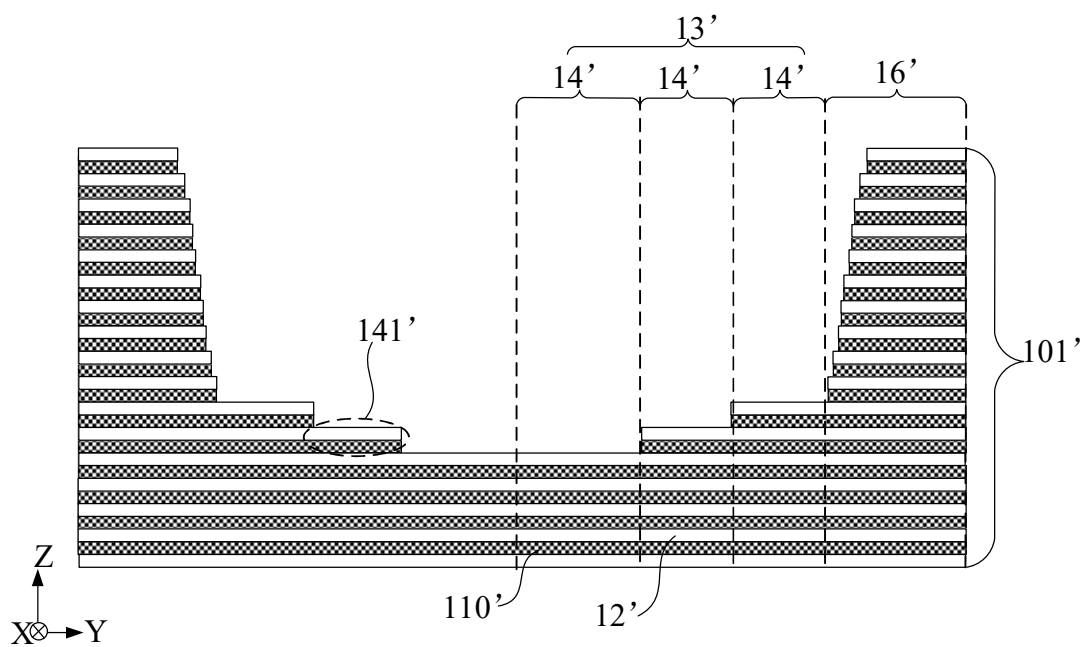


Fig. 60

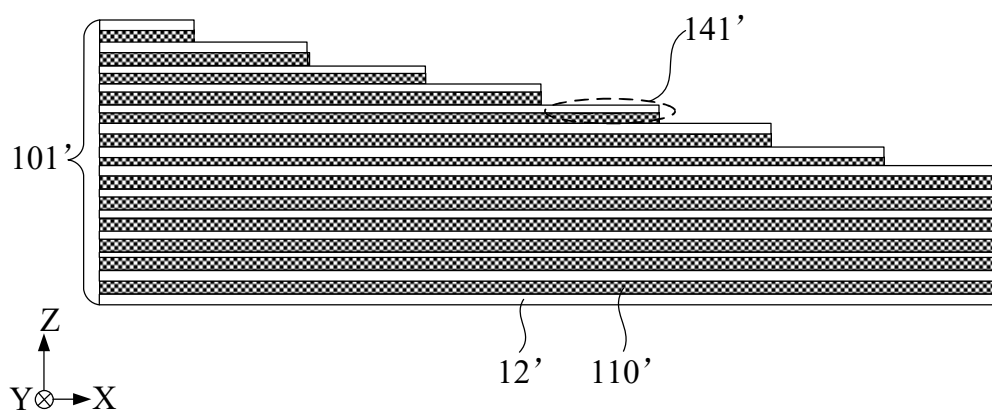


Fig. 61

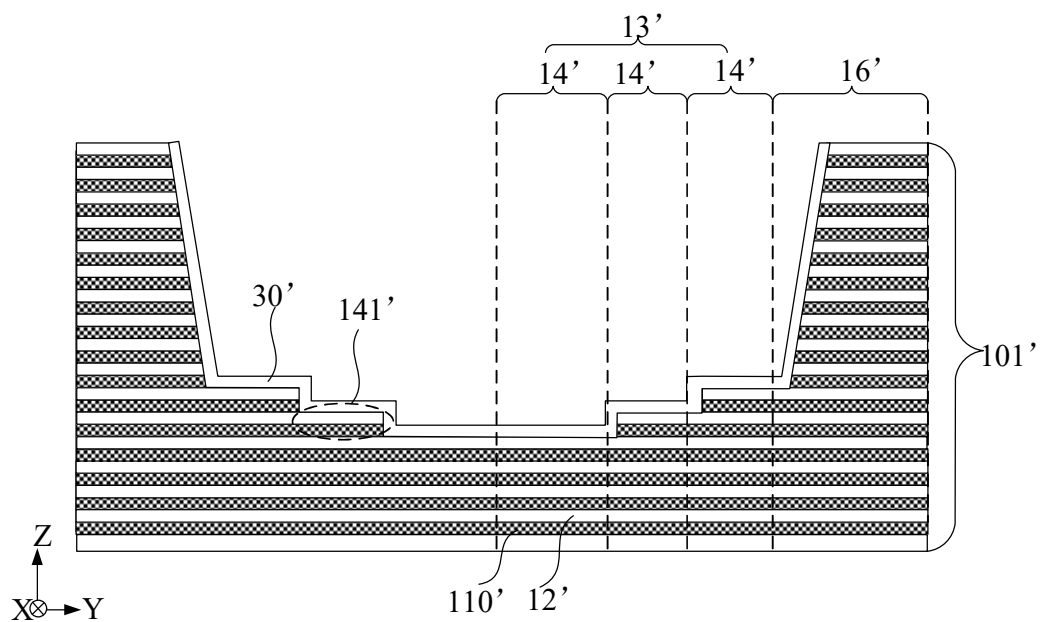


Fig. 62

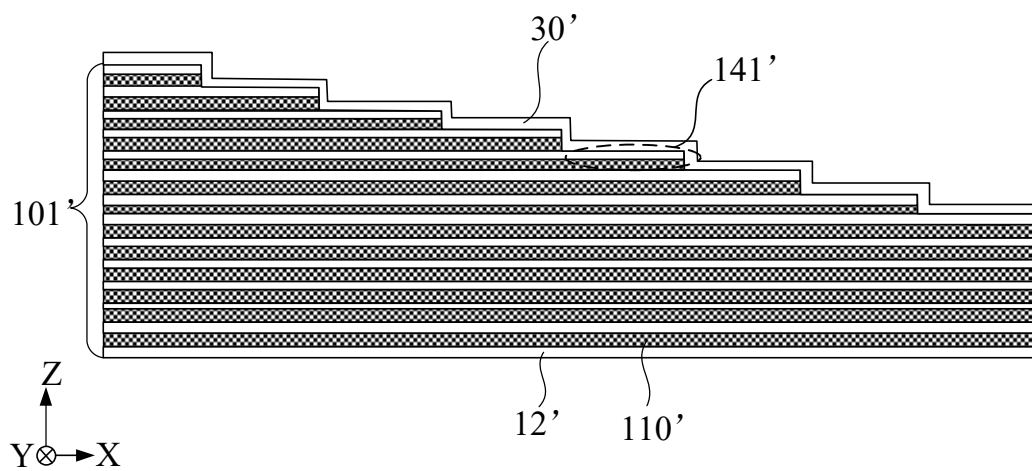
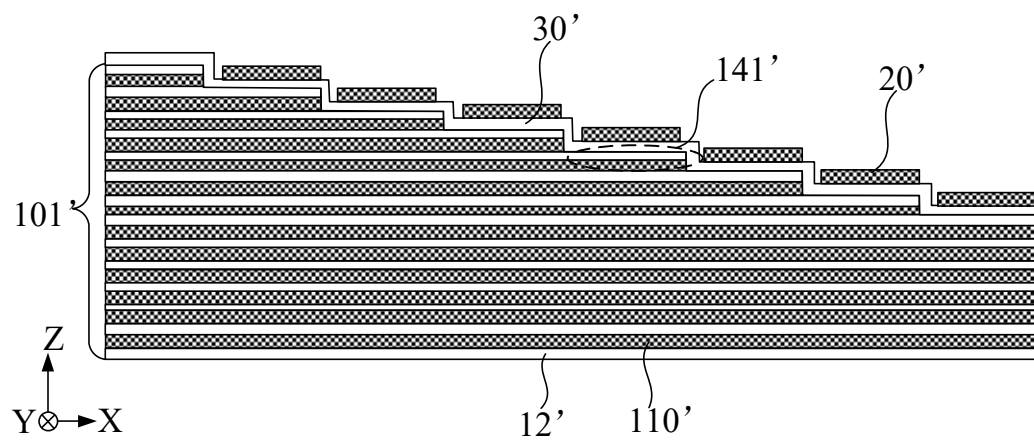
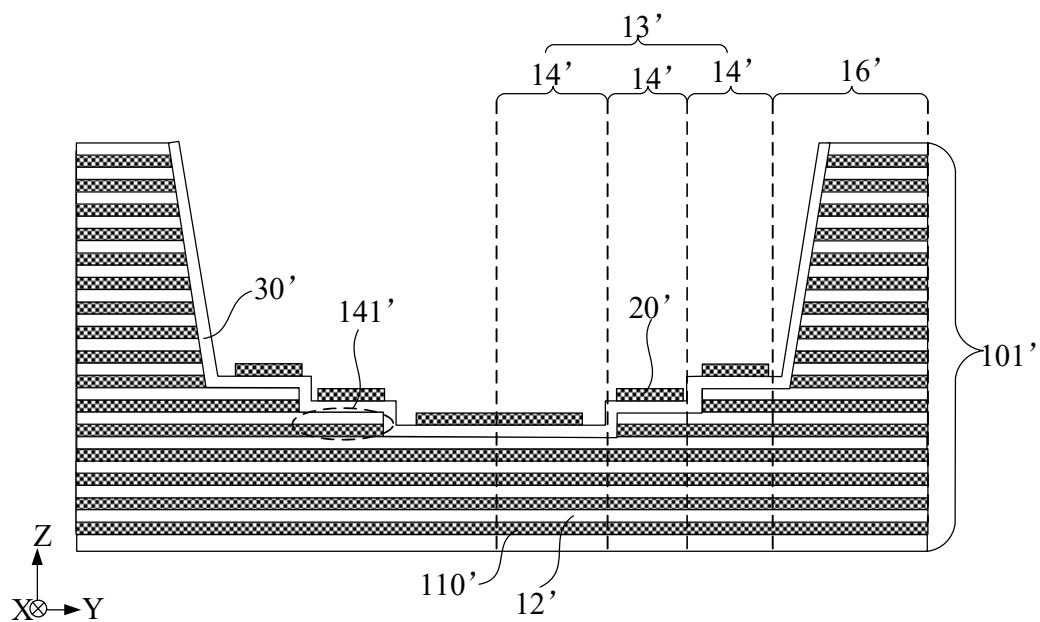


Fig. 63





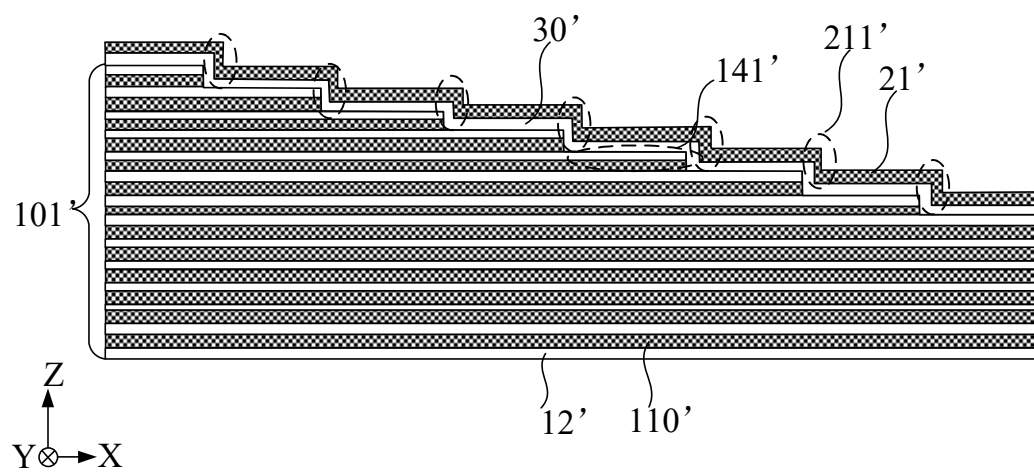


Fig. 68

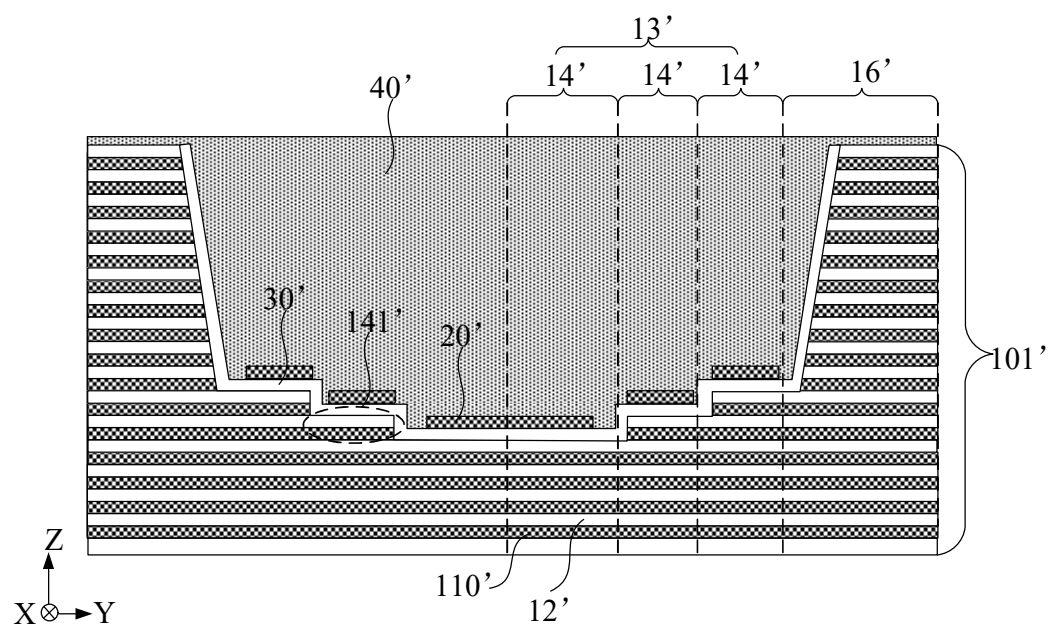


Fig. 69

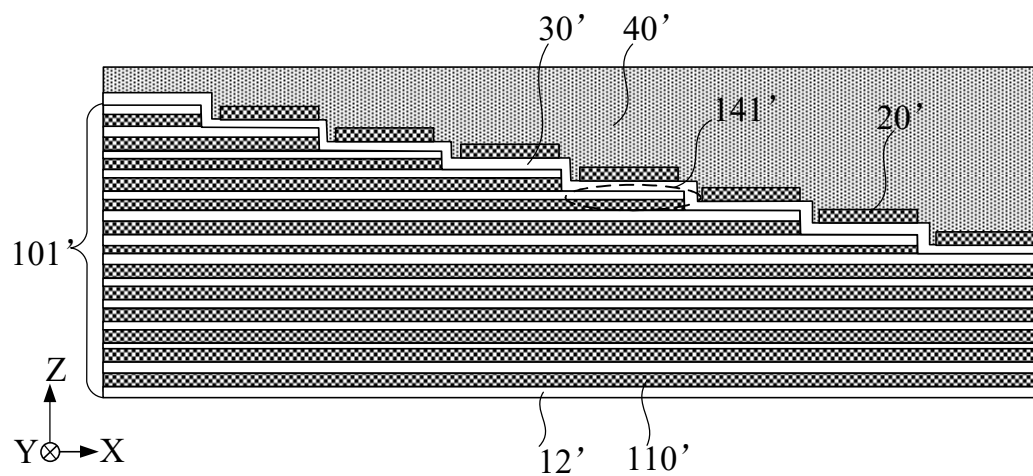


Fig. 70

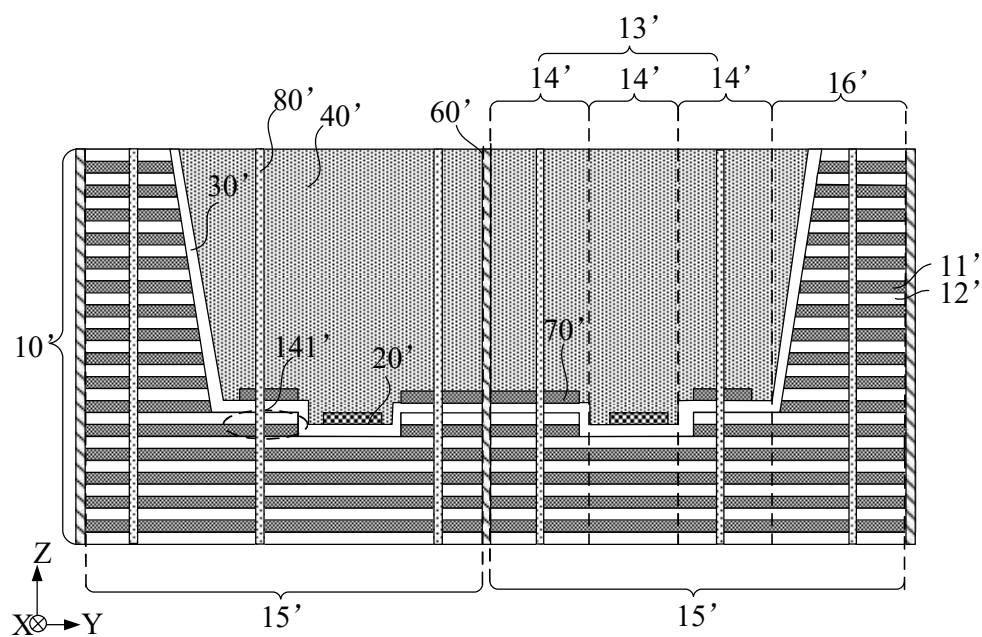


Fig. 71

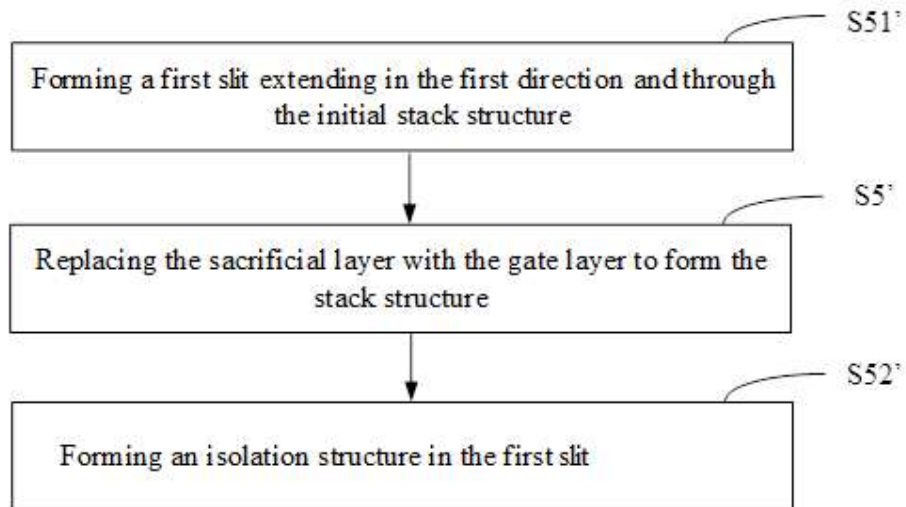


Fig. 72

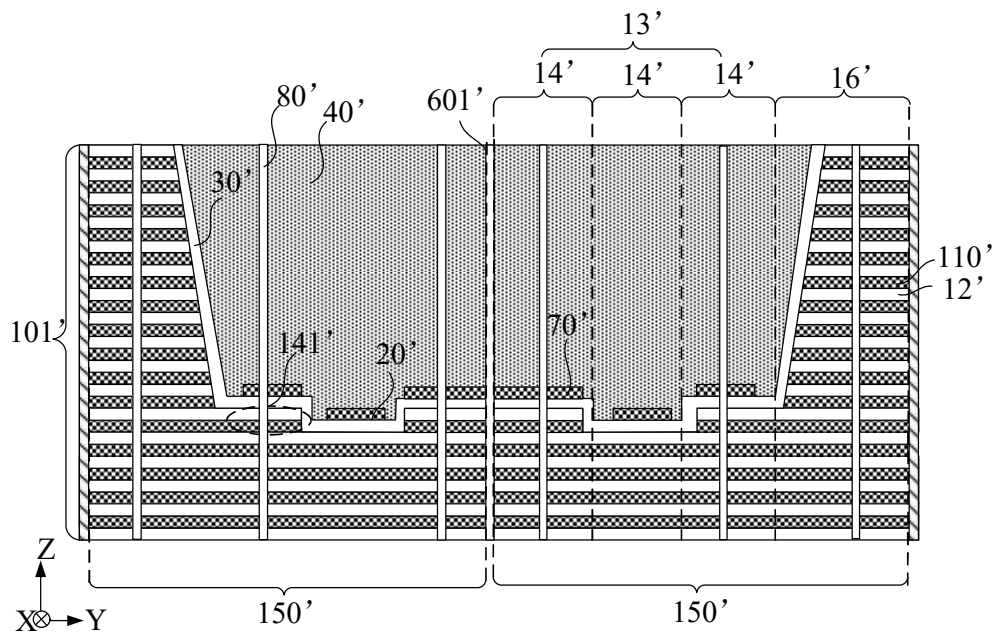


Fig. 73

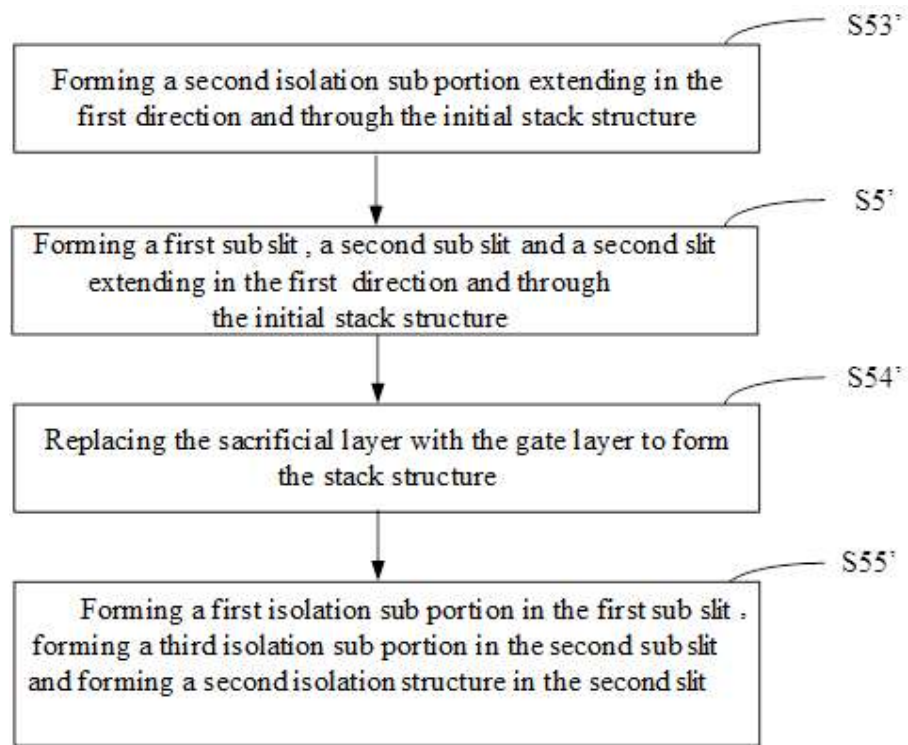


Fig. 74

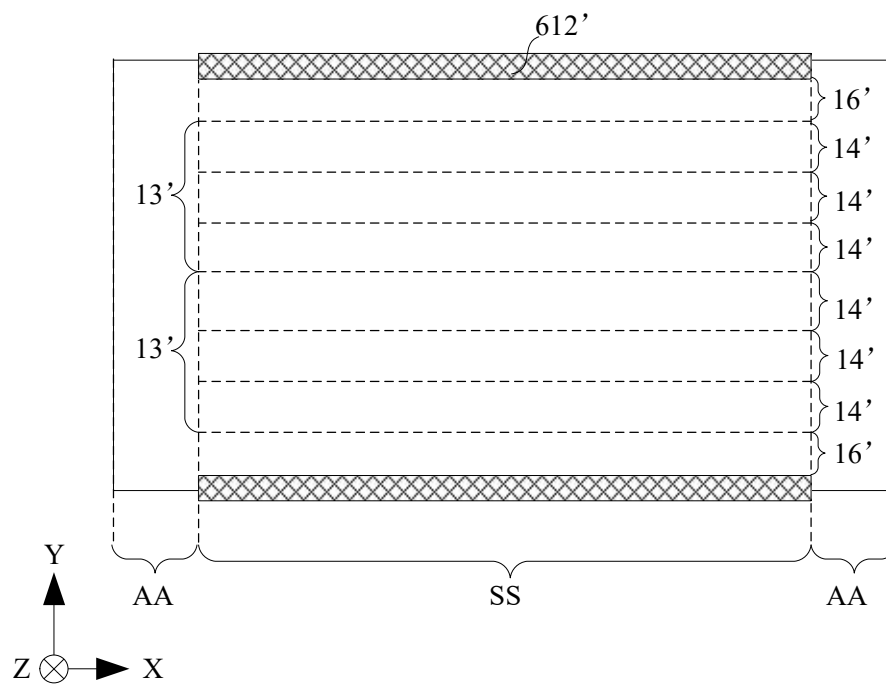


Fig. 75

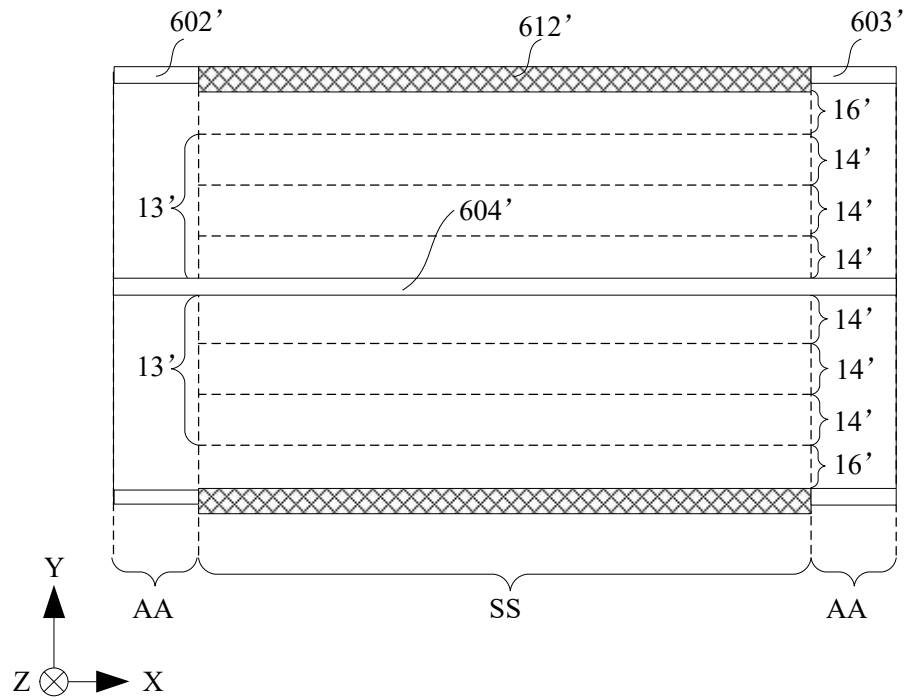


Fig. 76

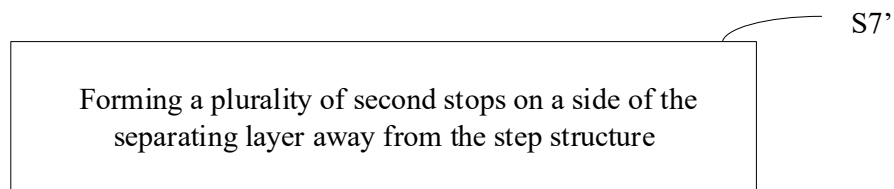


Fig. 77

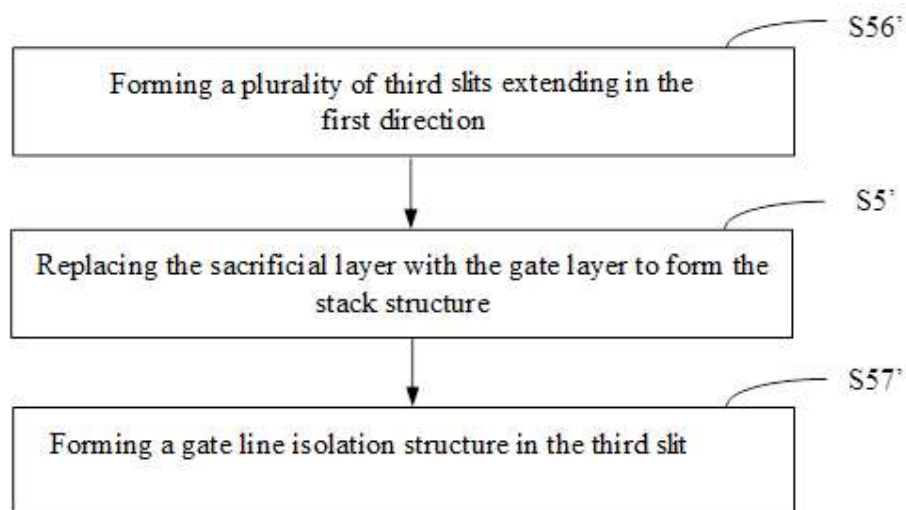


Fig. 78

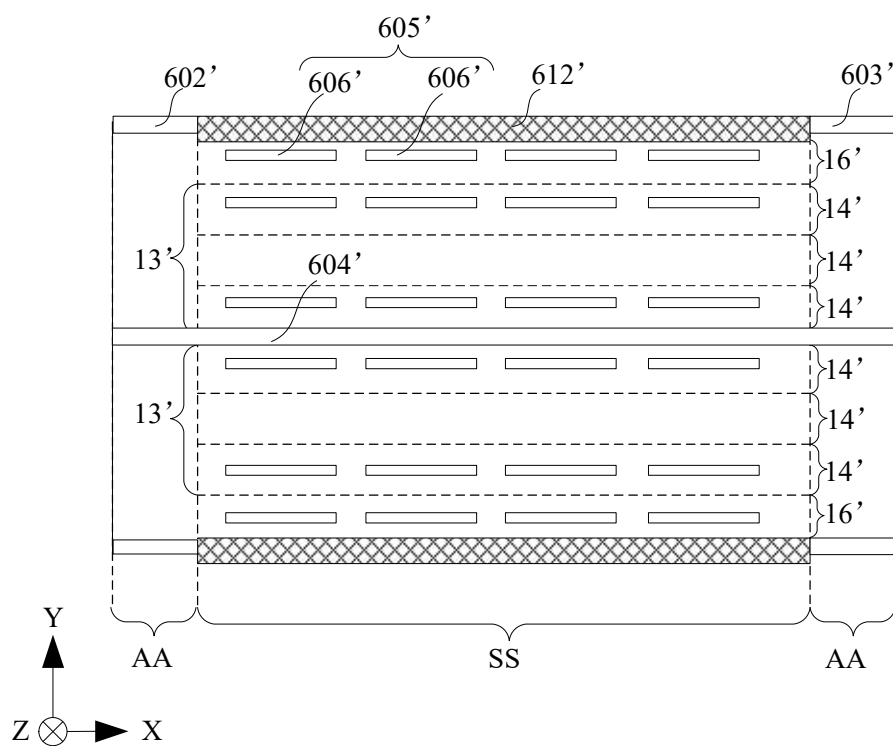


Fig. 79



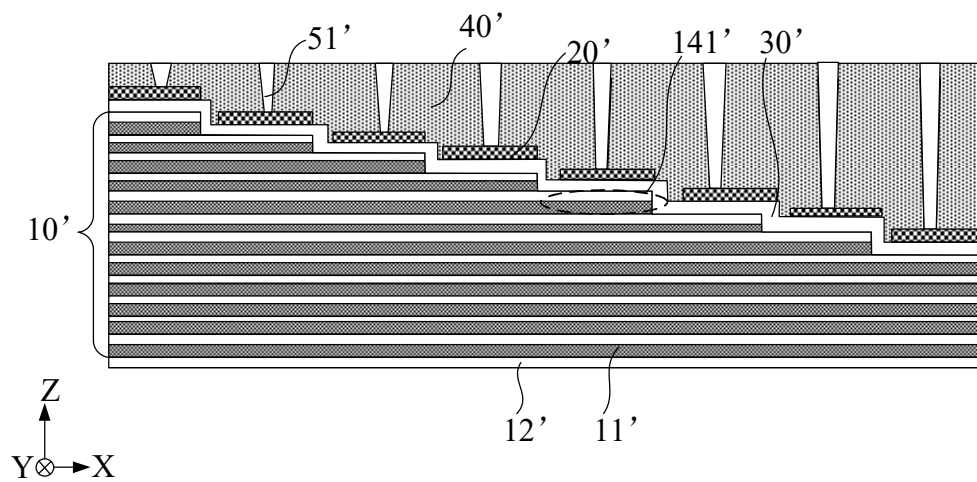


Fig. 82

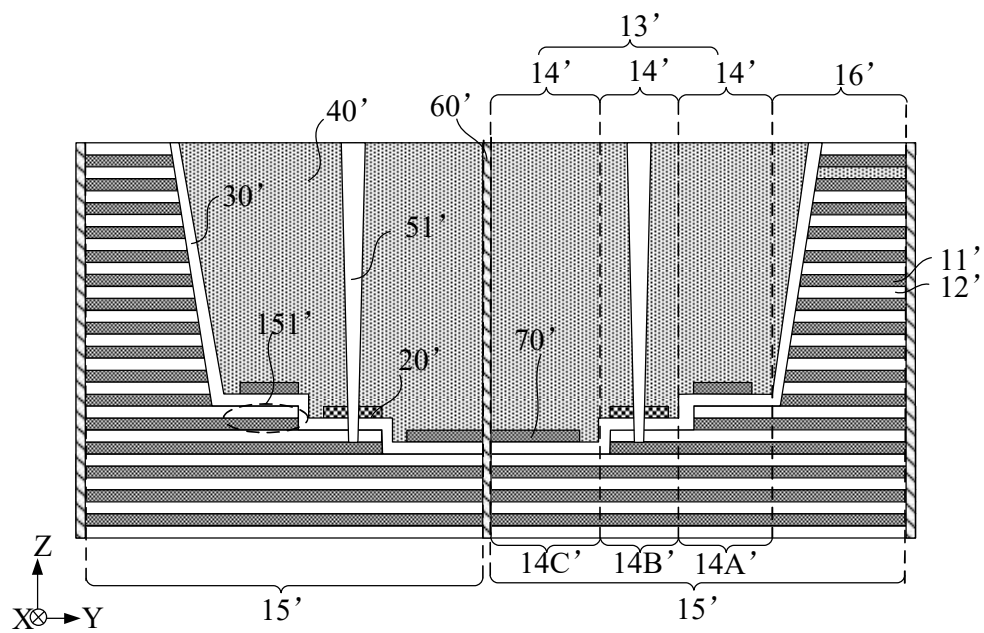


Fig. 83

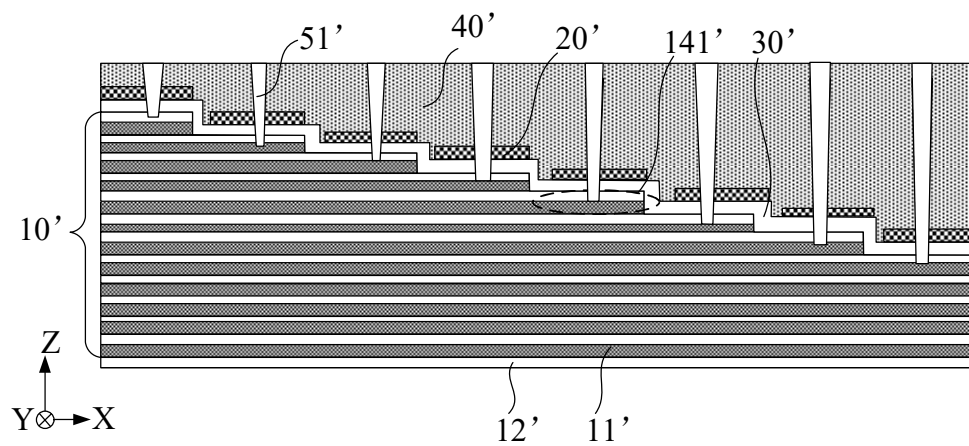


Fig. 84

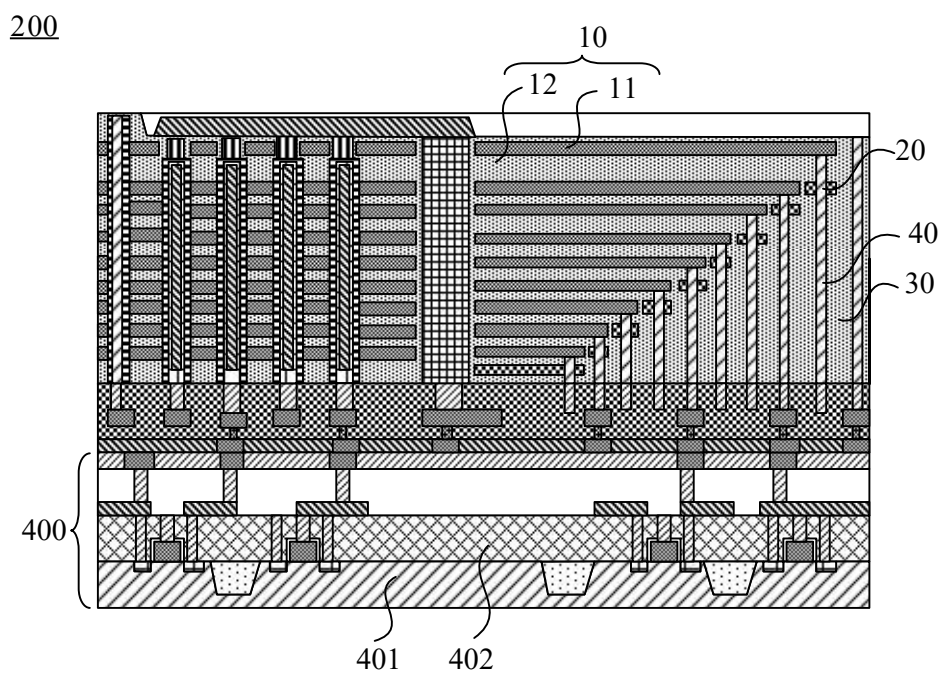


Fig. 85

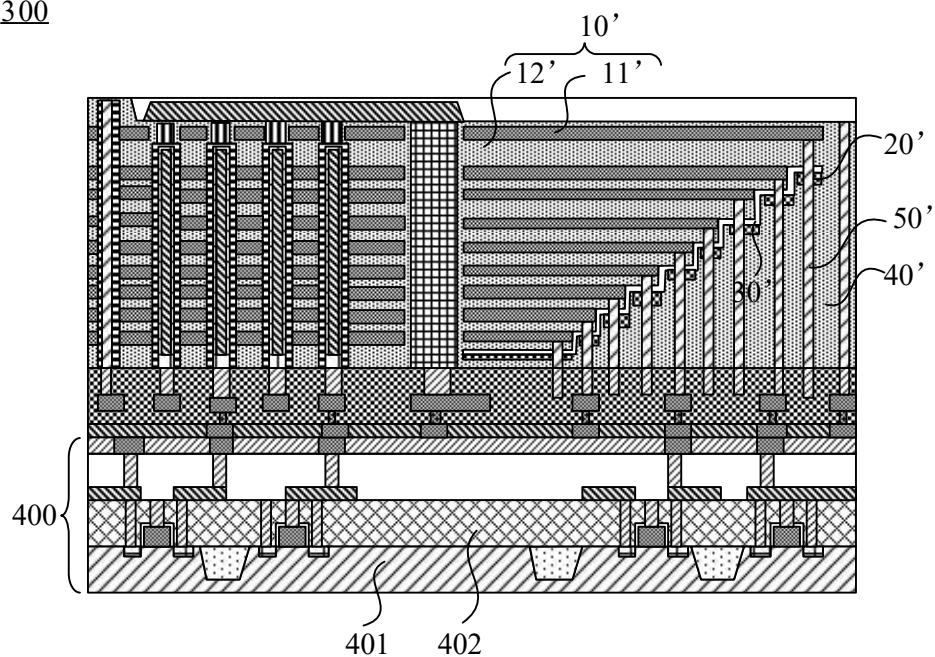
300

Fig. 86

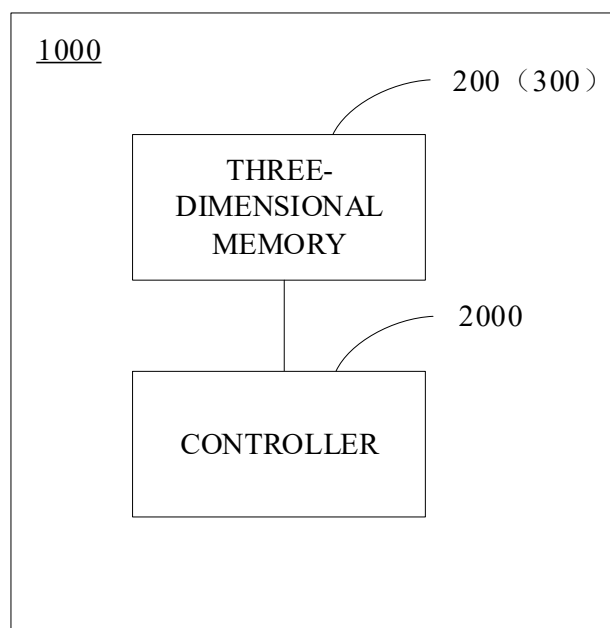


Fig. 87

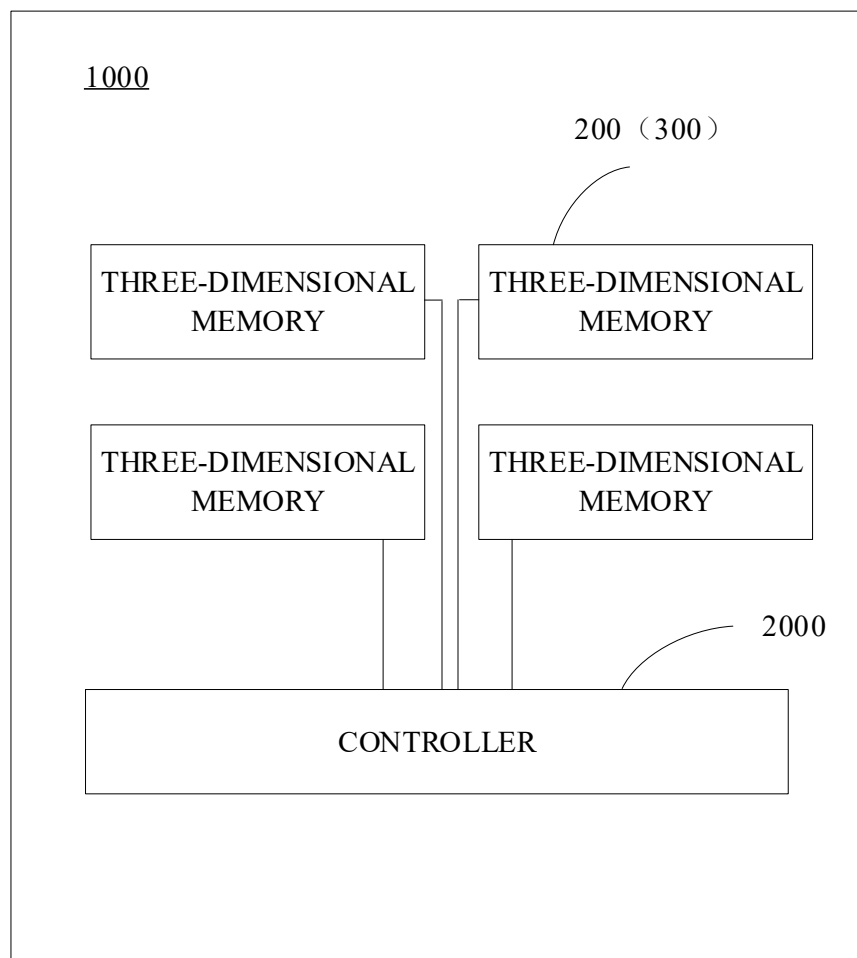


Fig. 88